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(54) **SILICON AND SILICON GERMANIUM NANOWIRE FORMATION**

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H01L 29/06 (2006.01)
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CPC **H01L 21/823821** (2013.01); **B82Y 10/00** (2013.01); **B82Y 40/00** (2013.01);
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See application file for complete search history.

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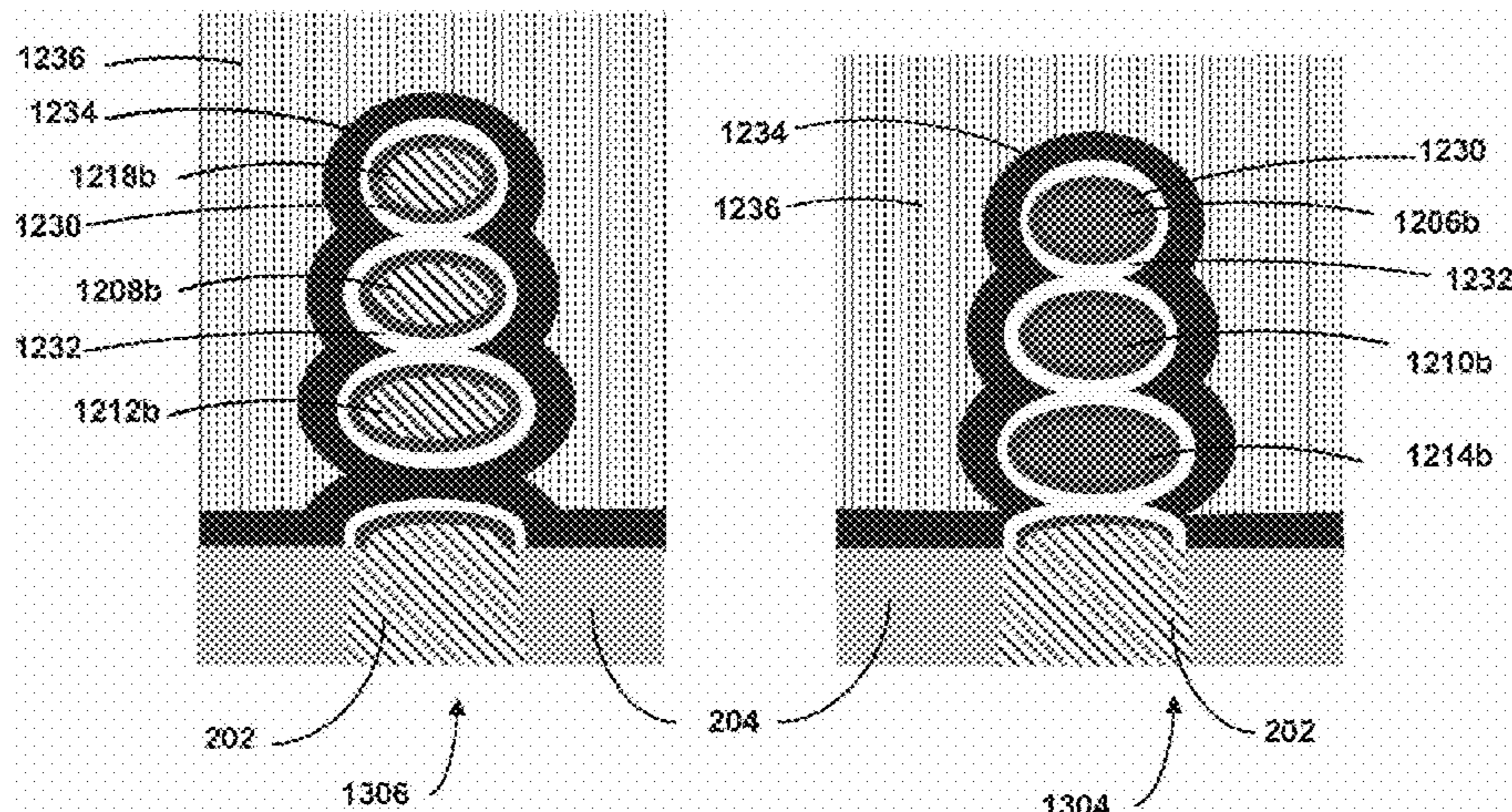
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(57) **ABSTRACT**

Among other things, one or semiconductor arrangements, and techniques for forming such semiconductor arrangements are provided. For example, one or more silicon and silicon germanium stacks are utilized to form PMOS transistors comprising germanium nanostructure channels and NMOS transistors comprising silicon nanostructure channels. In an example, a first silicon and silicon germanium stack is oxidized to transform silicon to silicon oxide regions, which are removed to form germanium nanostructure channels for PMOS transistors. In another example, silicon and germanium layers within a second silicon and silicon germanium stack are removed to form silicon nanostructure channels for NMOS transistors. PMOS transistors having germanium nanostructure channels and NMOS tran-

(Continued)



sisters having silicon nanostructure channels are formed as part of a single fabrication process.

20 Claims, 18 Drawing Sheets

Related U.S. Application Data

which is a continuation of application No. 16/205,419, filed on Nov. 30, 2018, now Pat. No. 10,699,964, which is a continuation of application No. 15/924,350, filed on Mar. 19, 2018, now Pat. No. 10,163,729, which is a continuation of application No. 15/463,326, filed on Mar. 20, 2016, now Pat. No. 9,935,016, which is a continuation of application No. 14/929,504, filed on Nov. 2, 2015, now Pat. No. 9,634,091, which is a division of application No. 13/971,239, filed on Aug. 20, 2013, now Pat. No. 9,184,269.

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- H01L 29/66* (2006.01)
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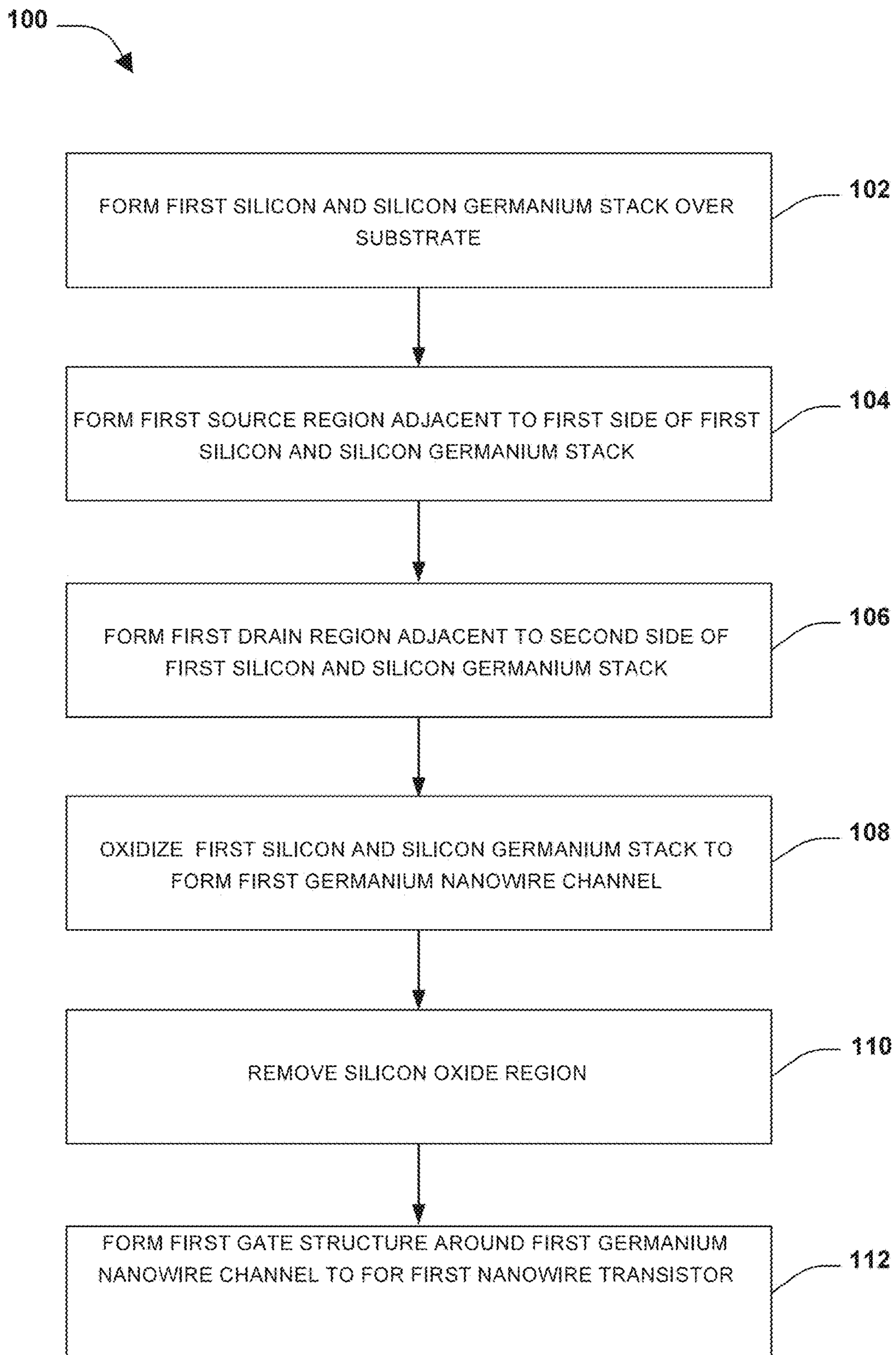


FIG. 1

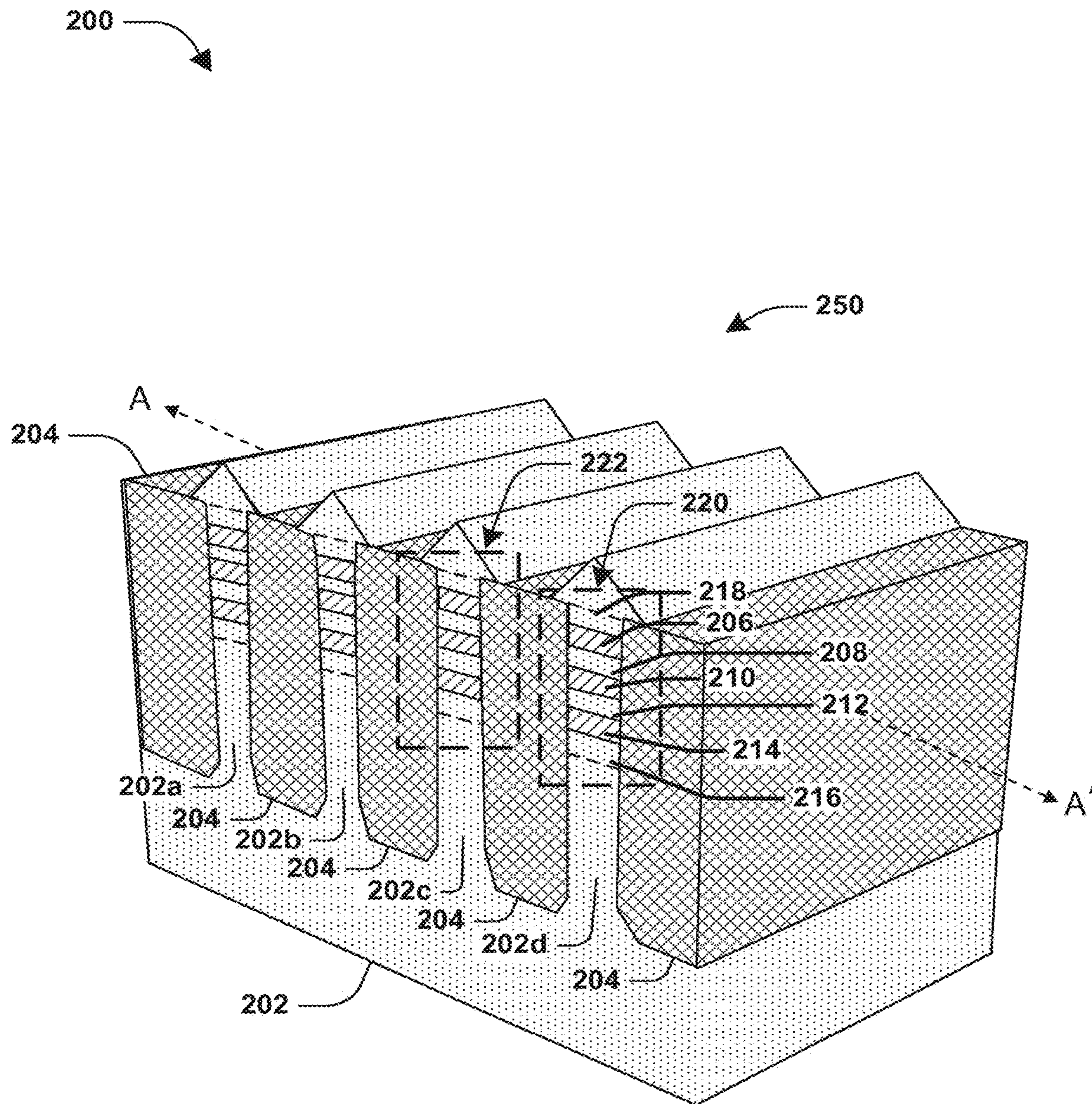


FIG. 2

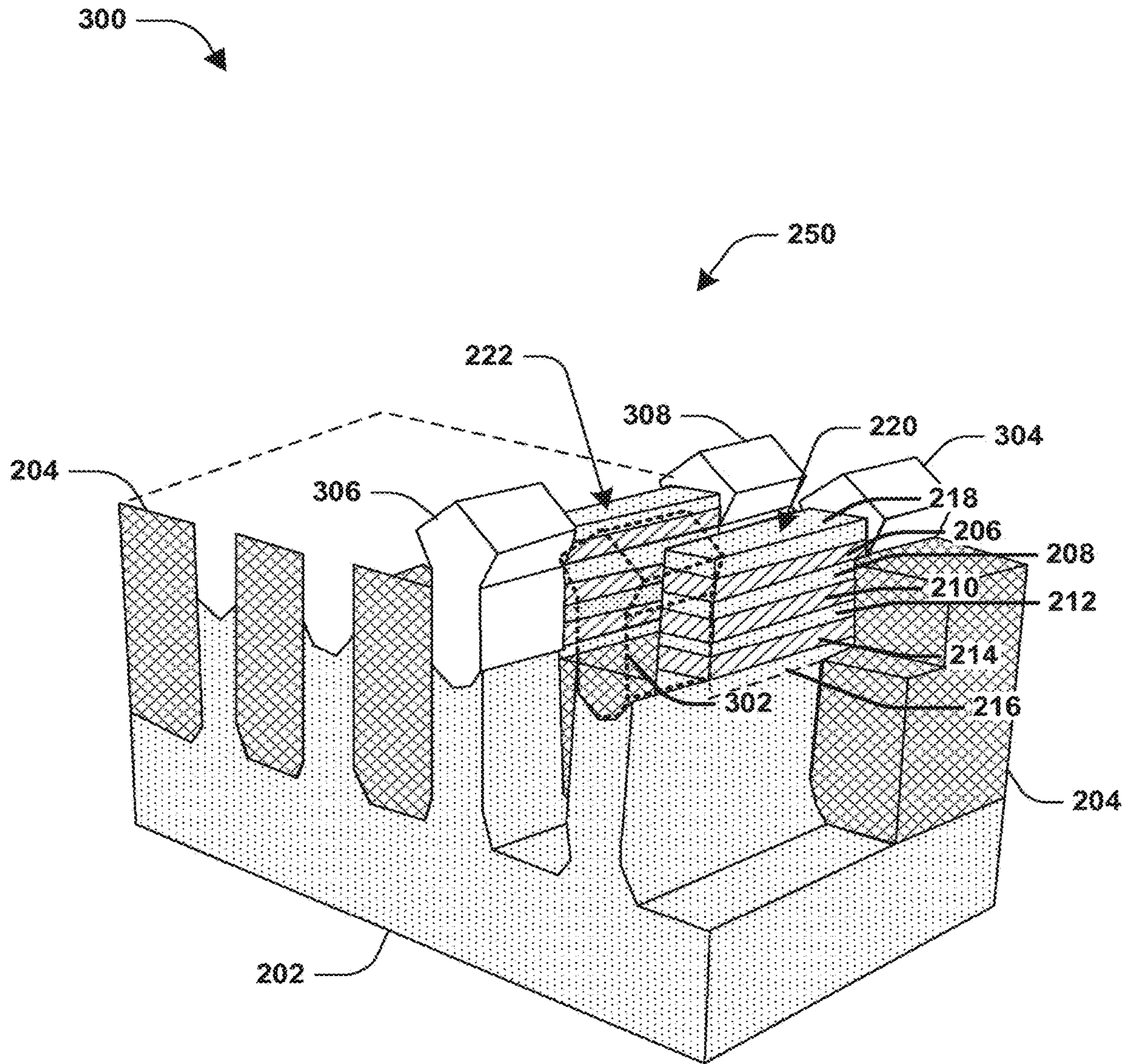


FIG. 3

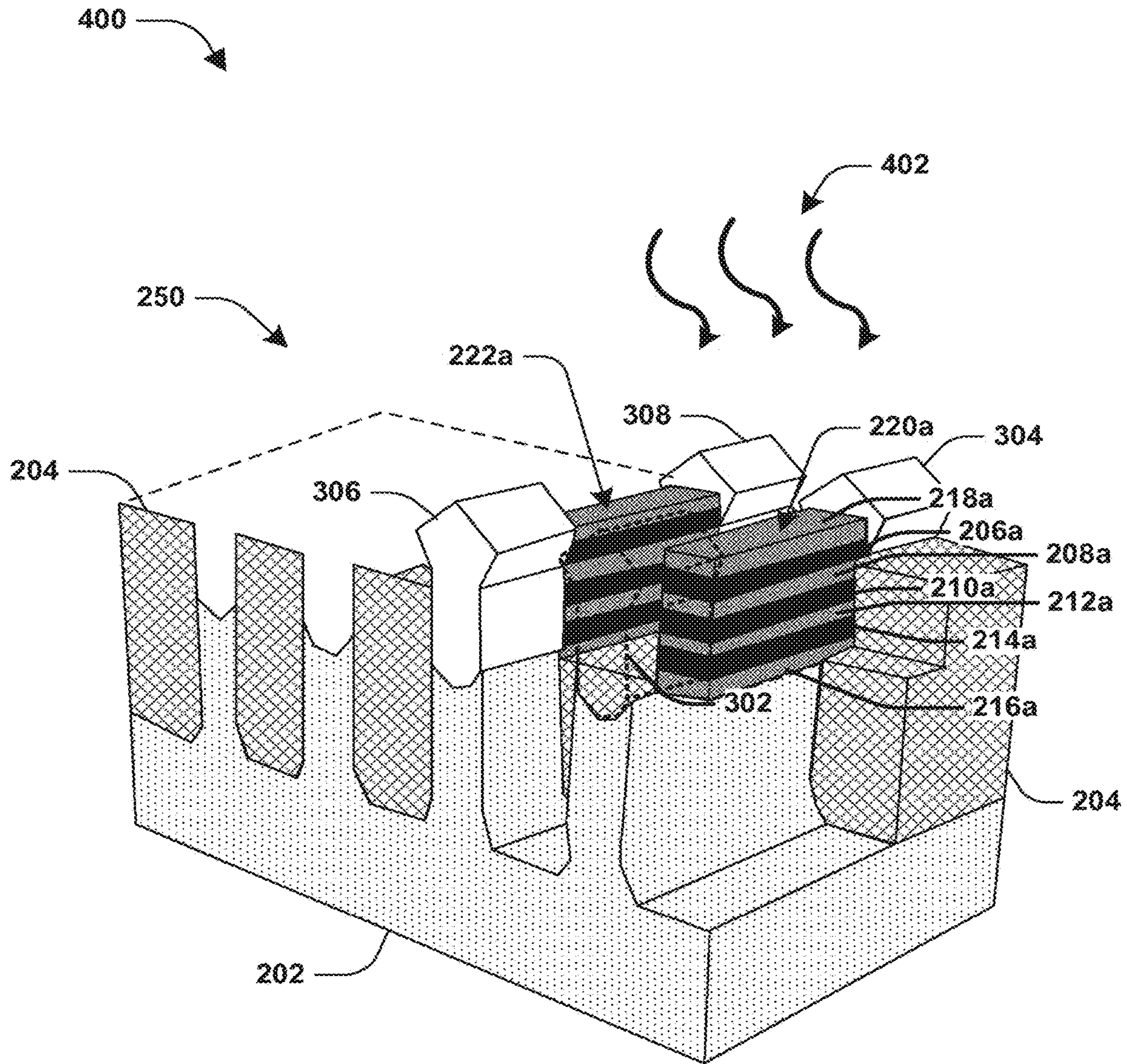


FIG. 4

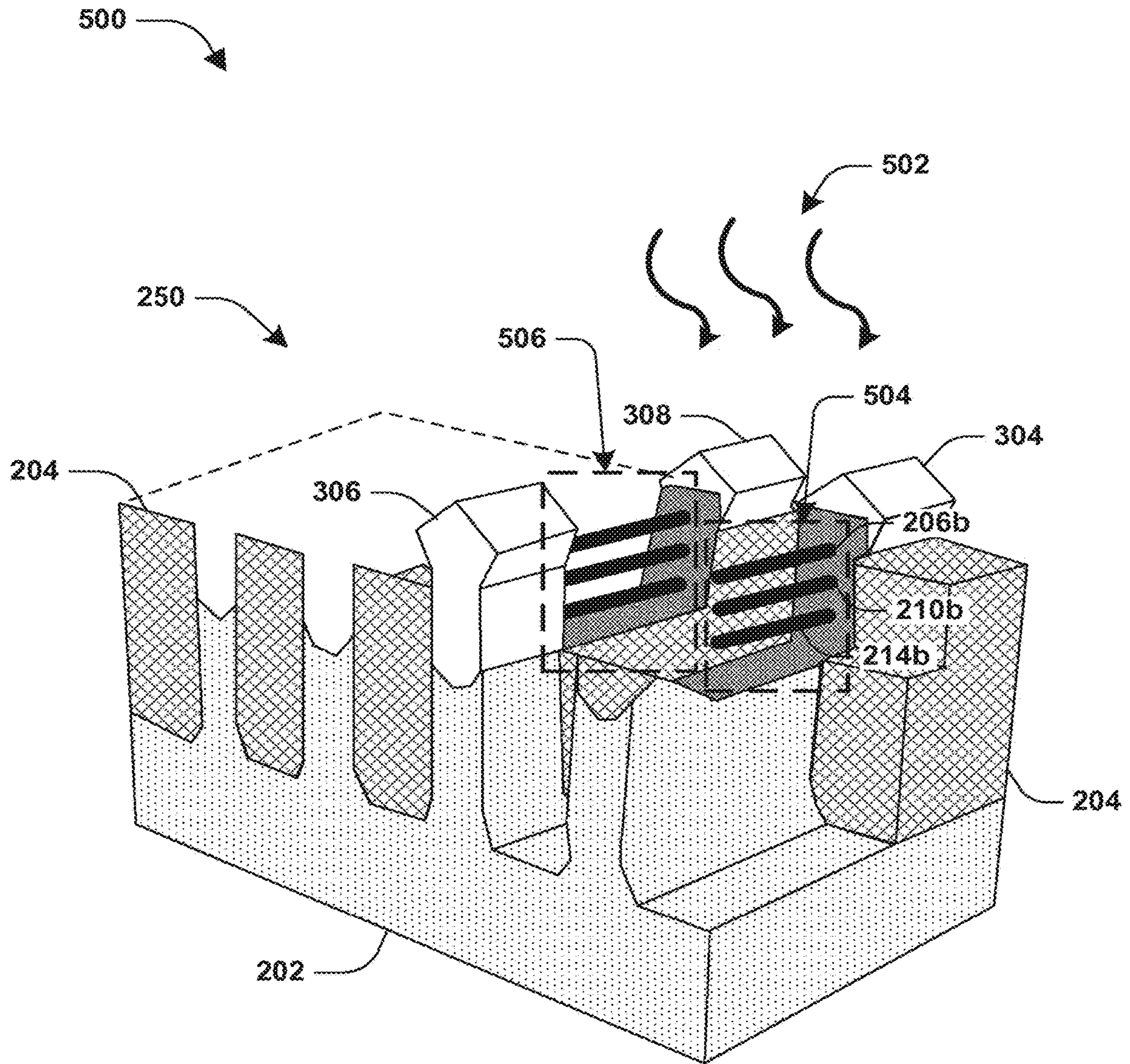


FIG. 5

600

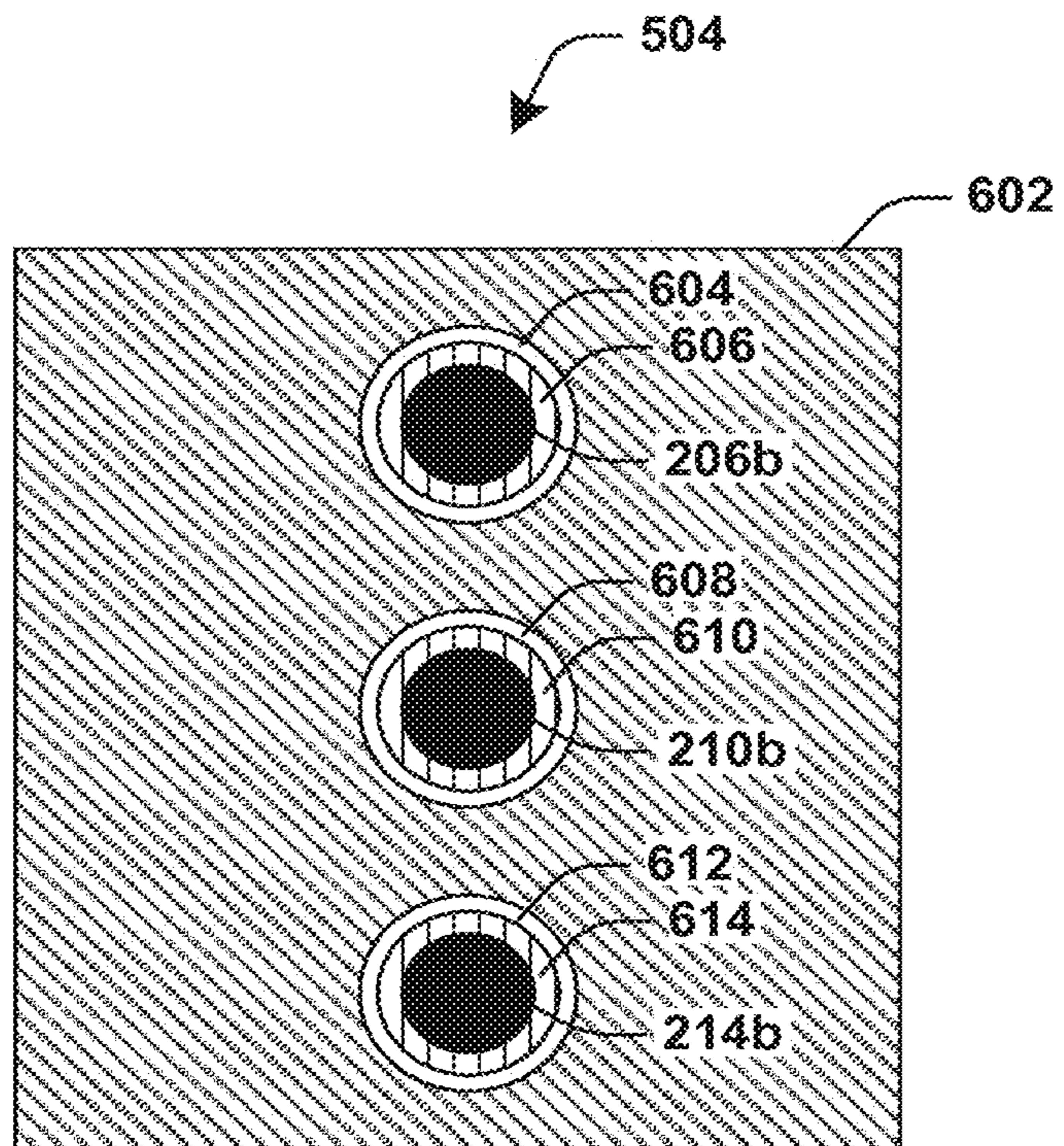


FIG. 6

700

504

706

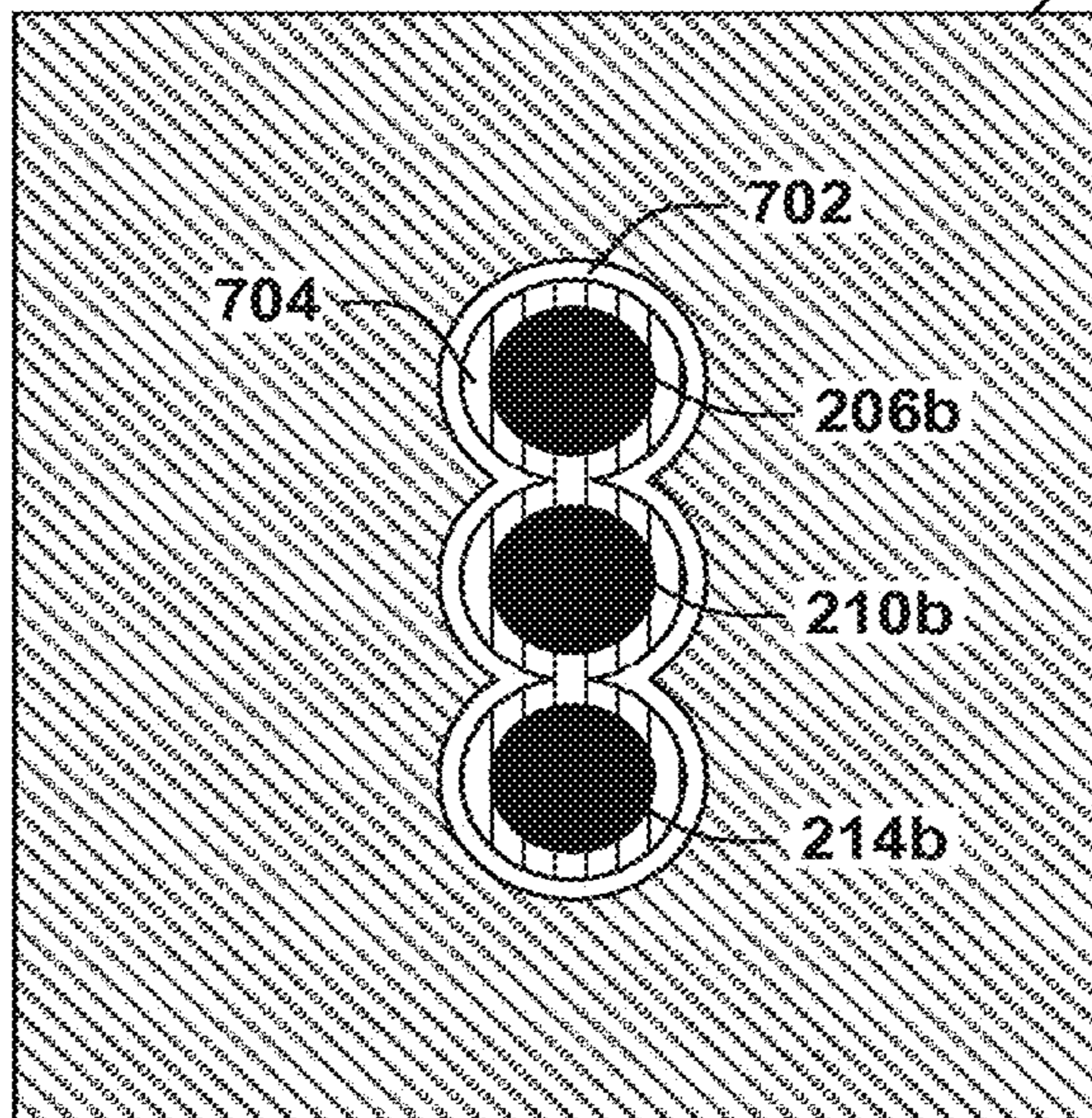


FIG. 7

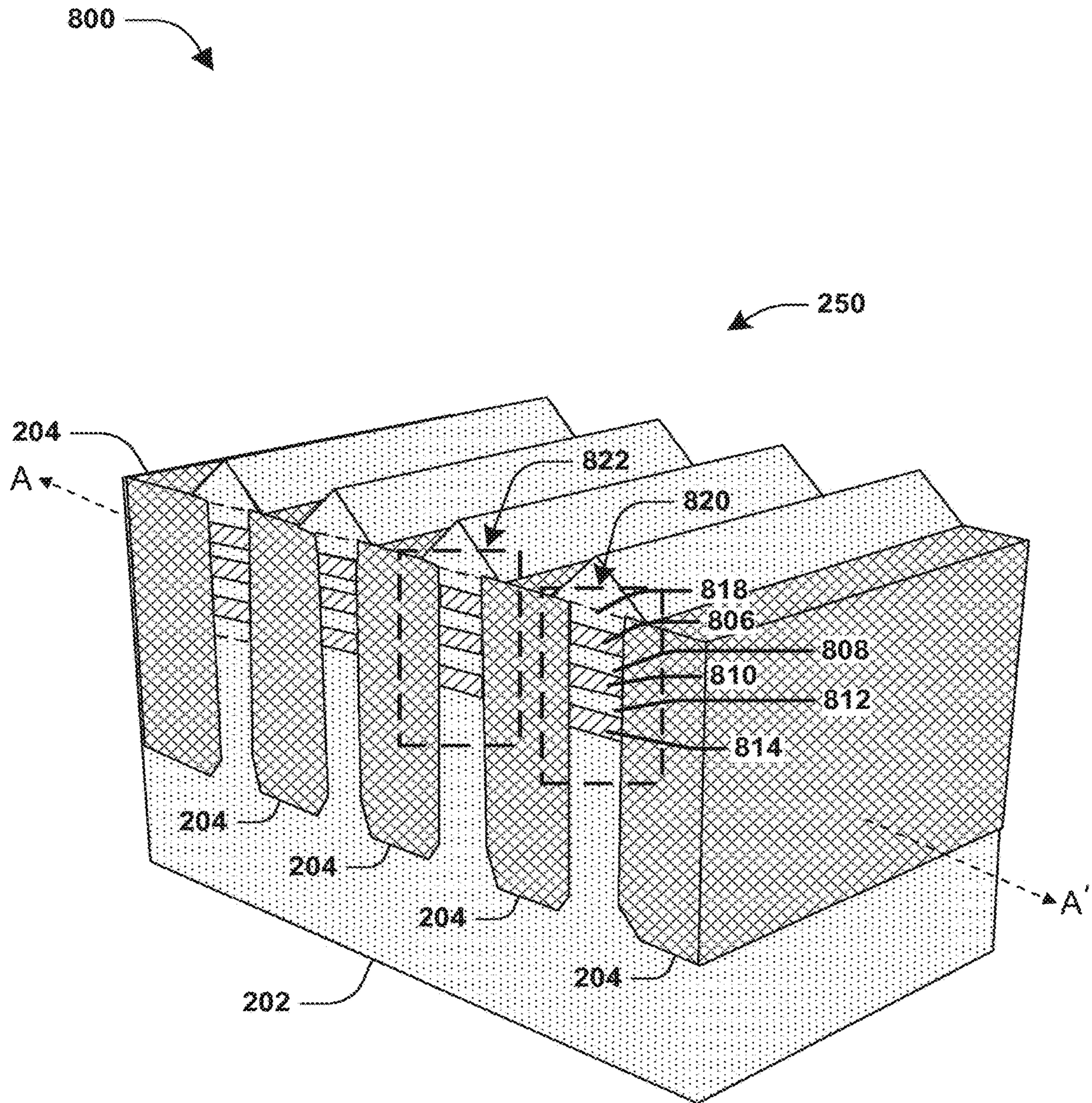


FIG. 8

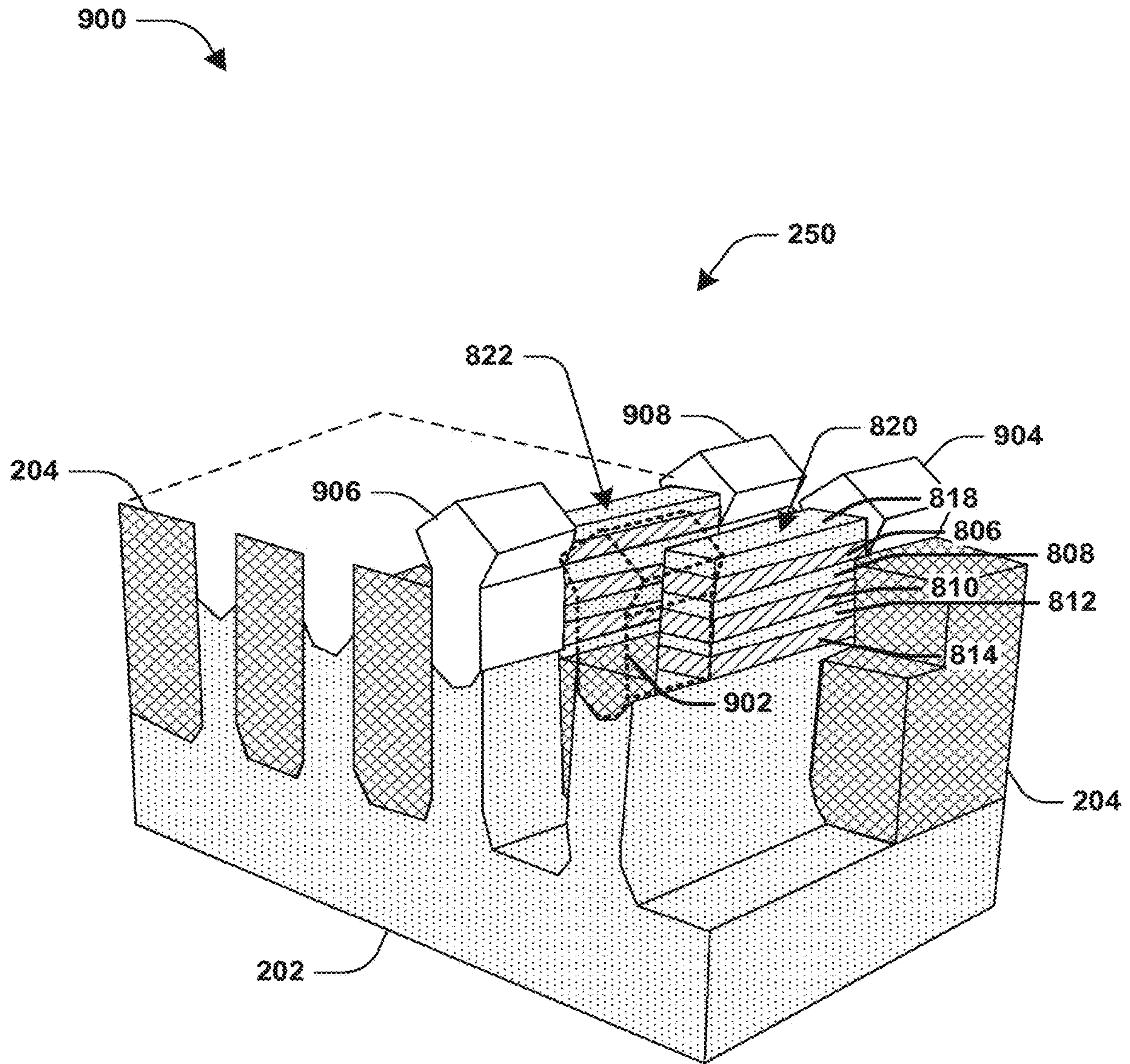


FIG. 9

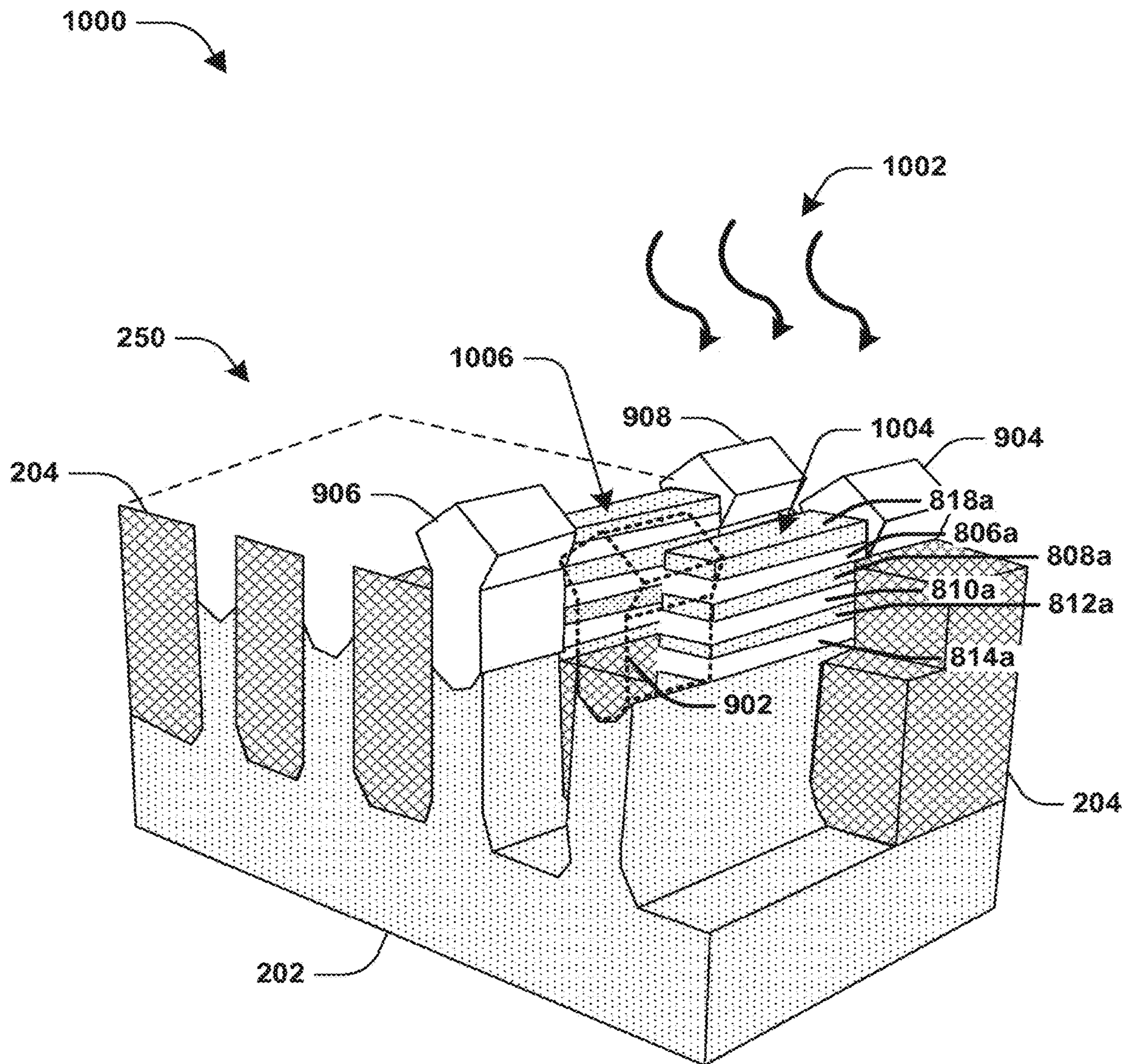


FIG. 10

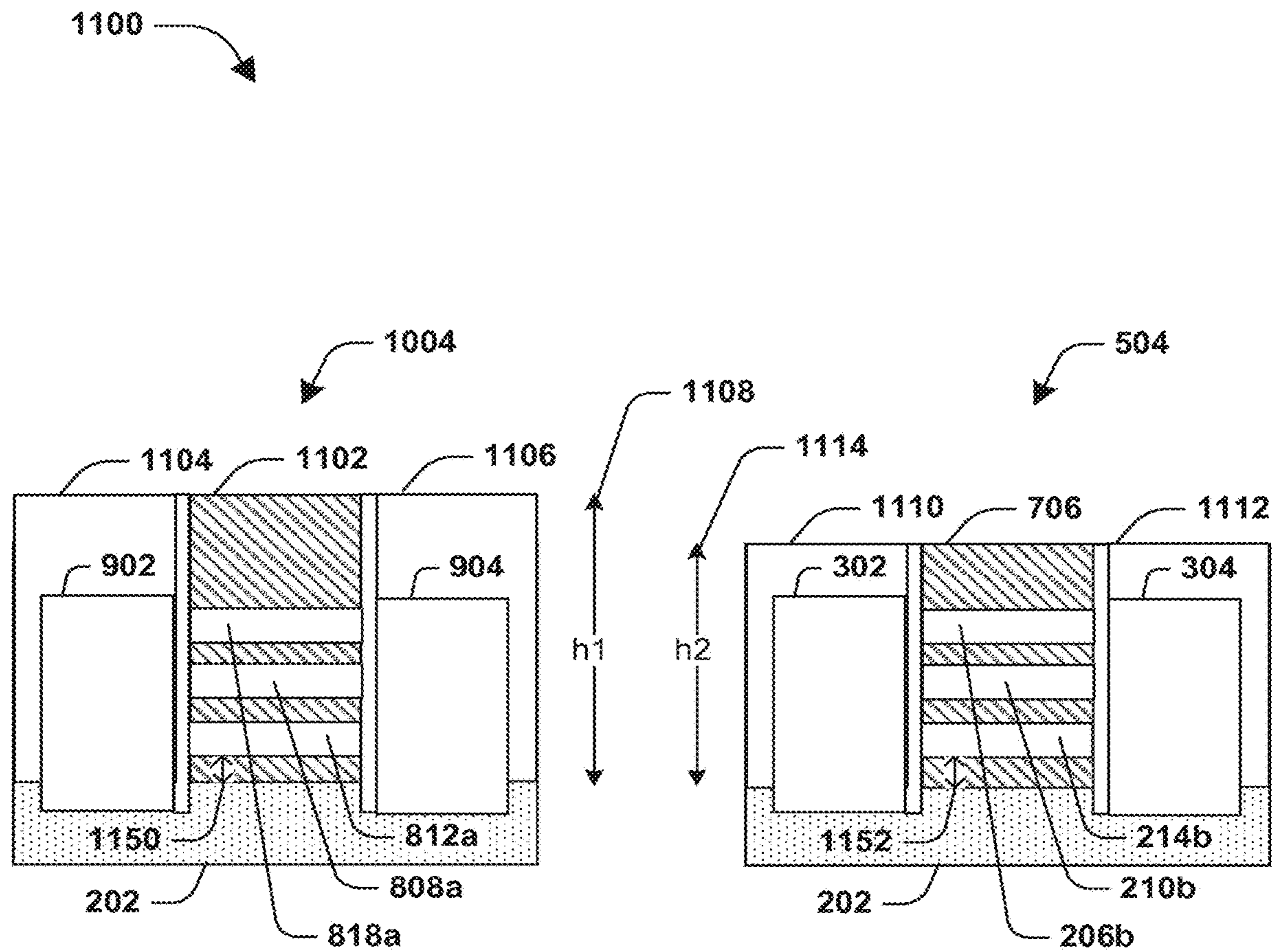


FIG. 11

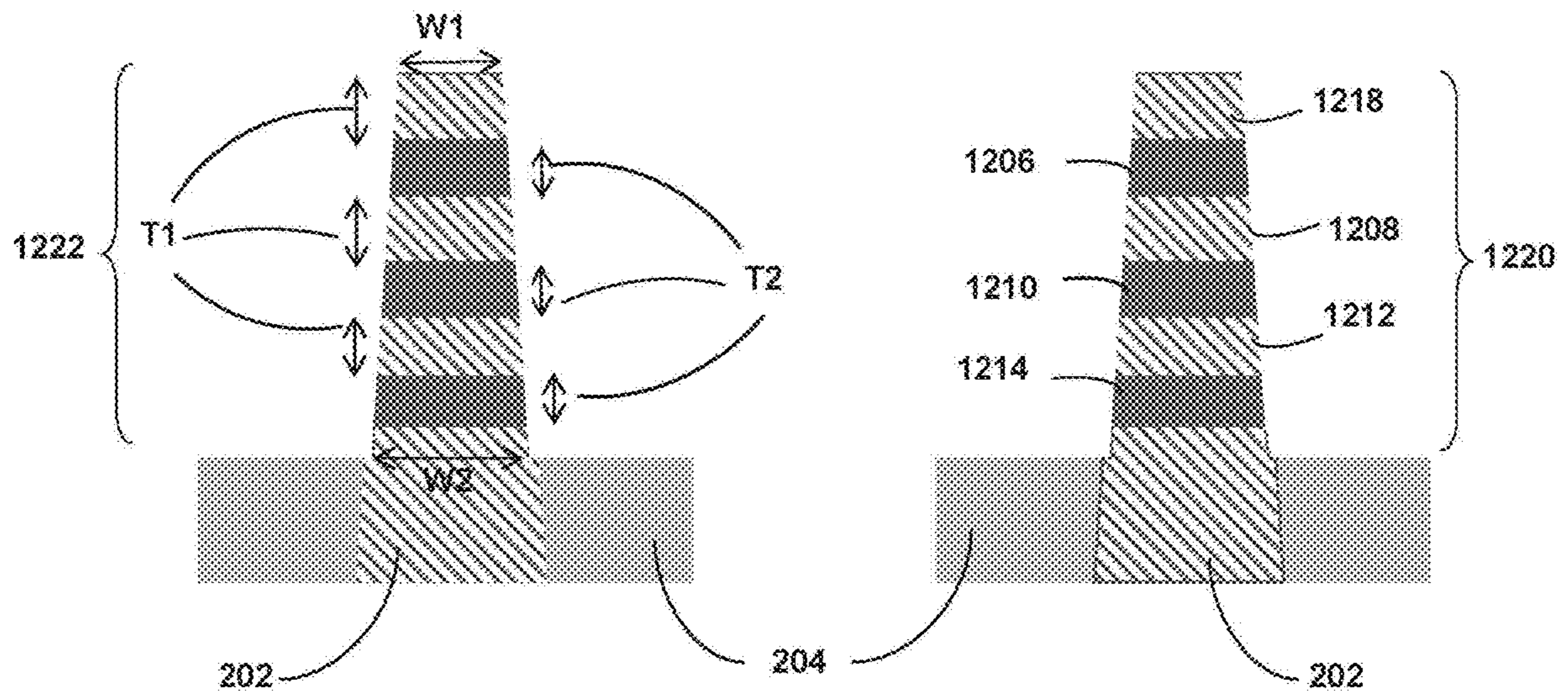


FIG.12

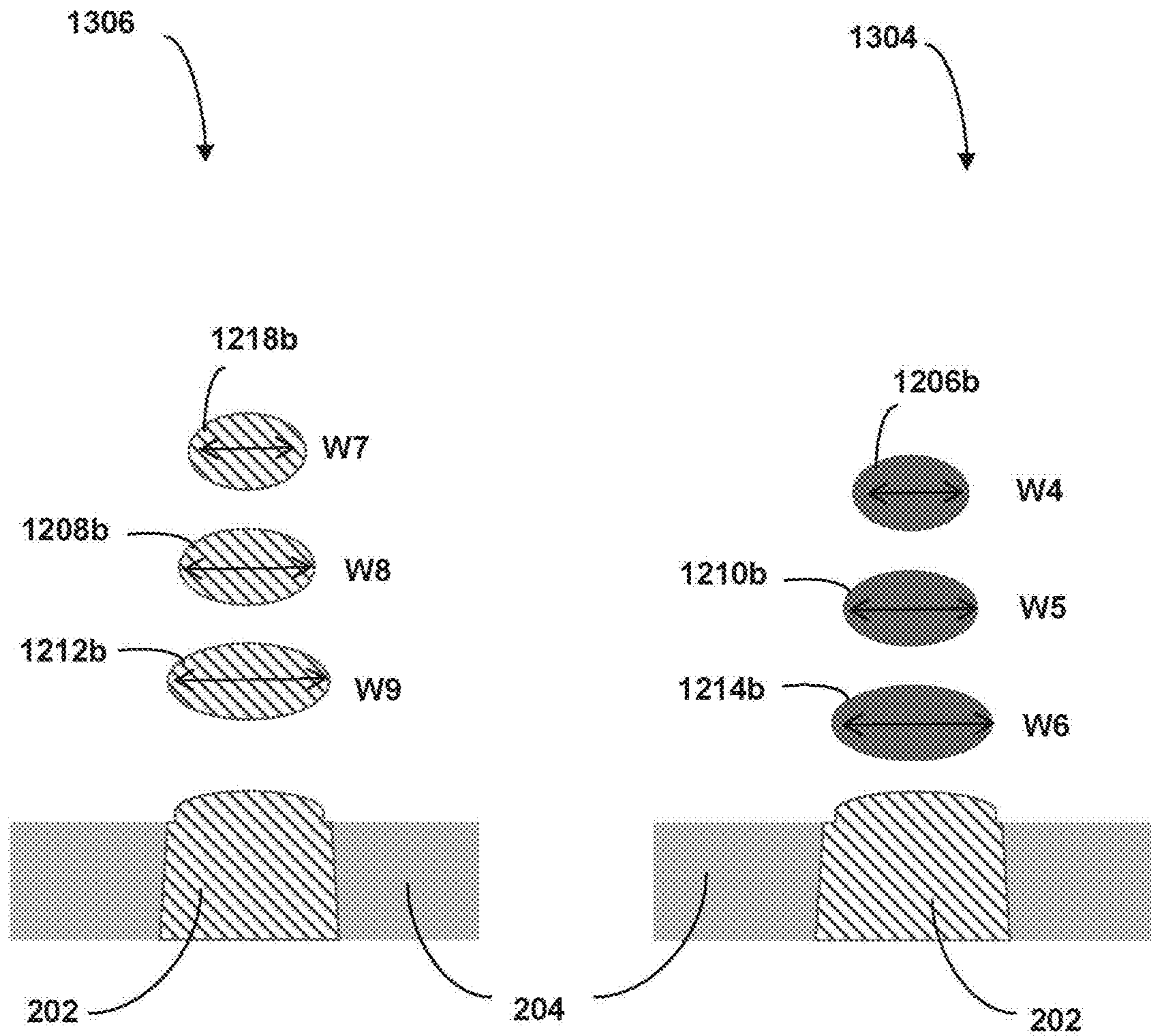


FIG.13

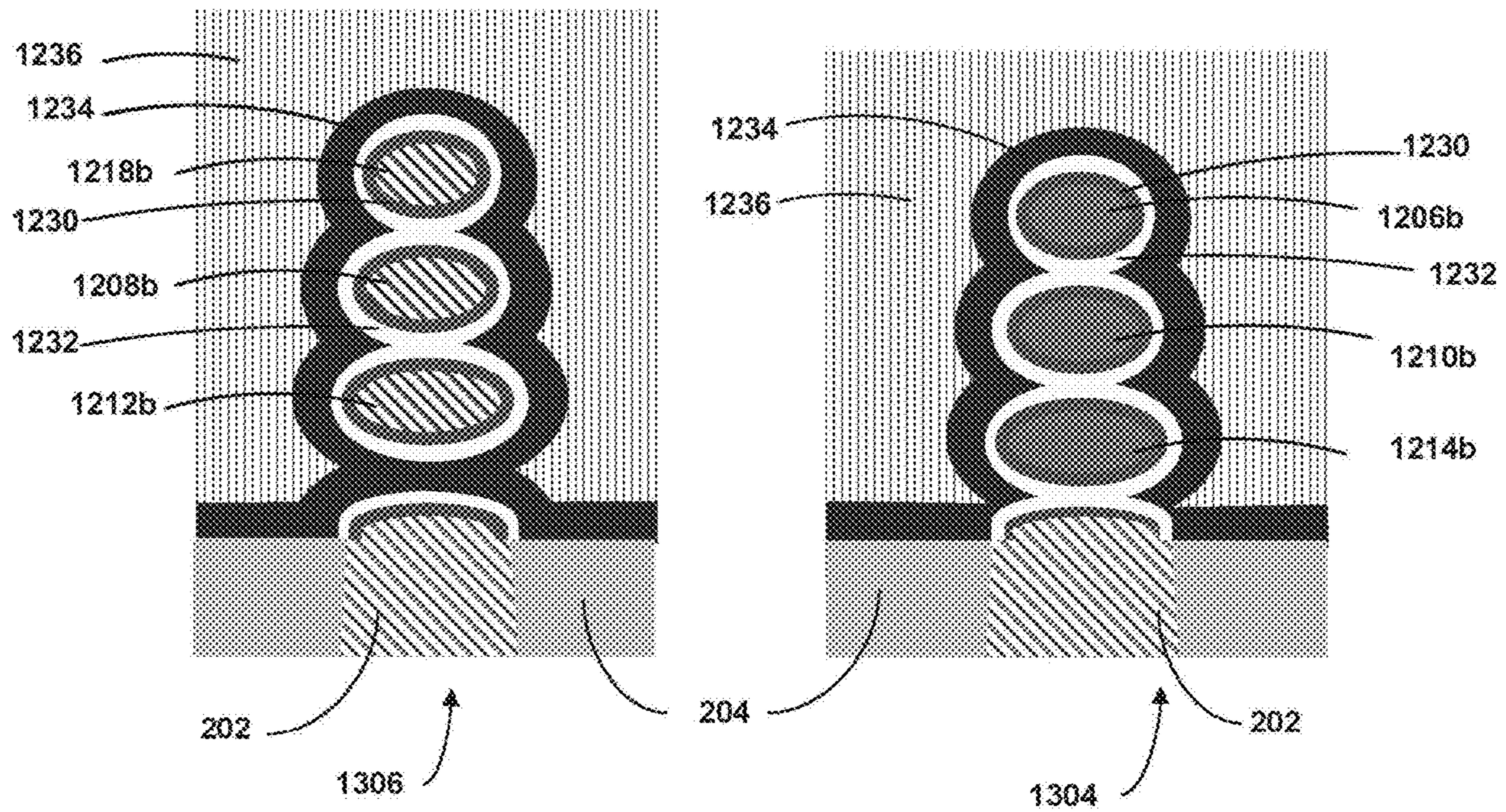


FIG.14

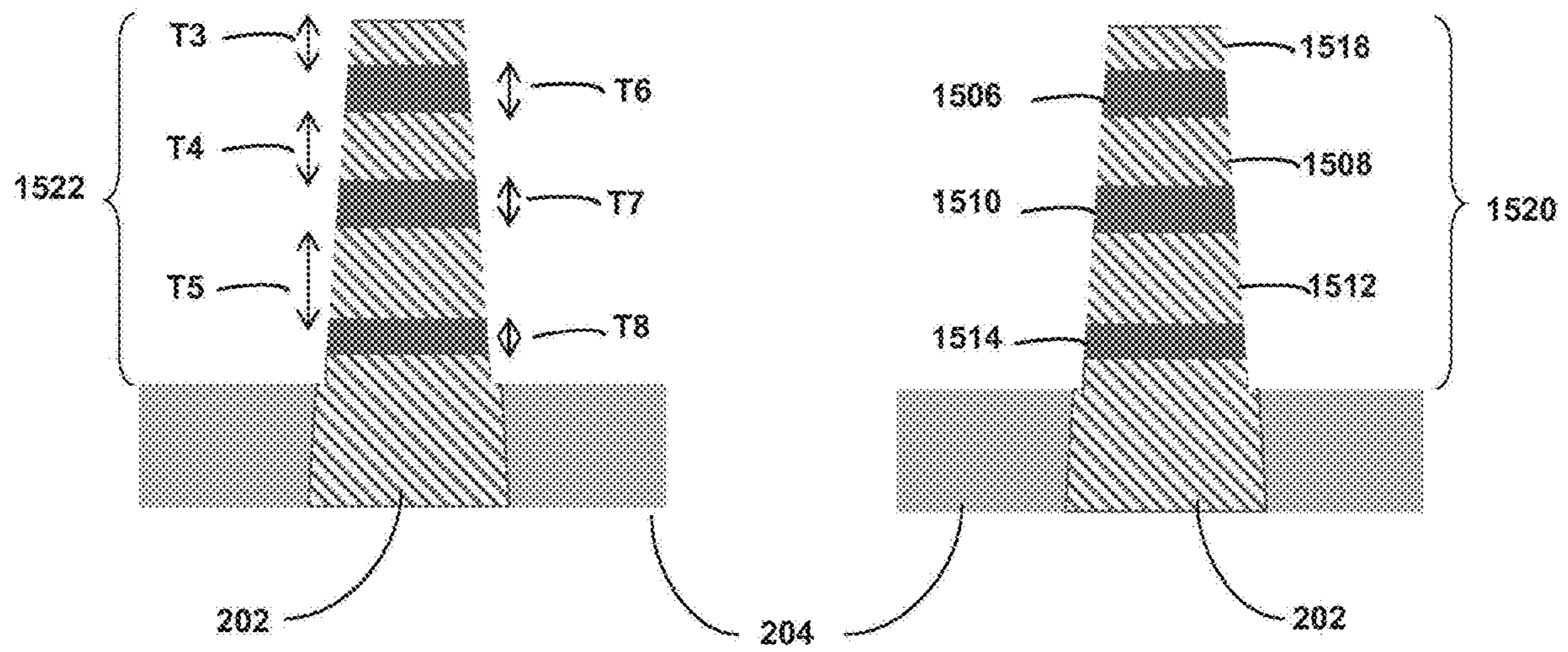


FIG.15

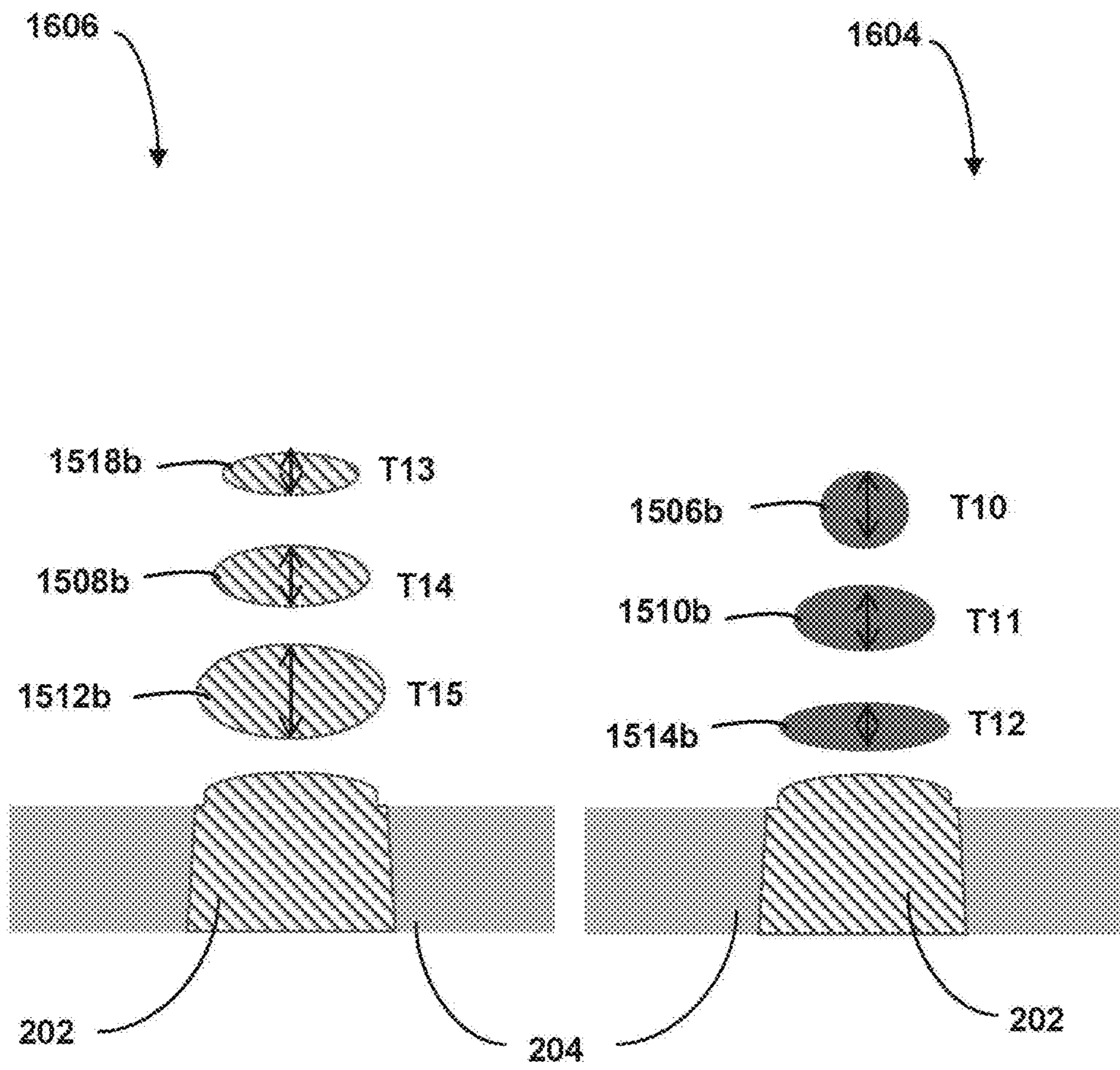


FIG.16

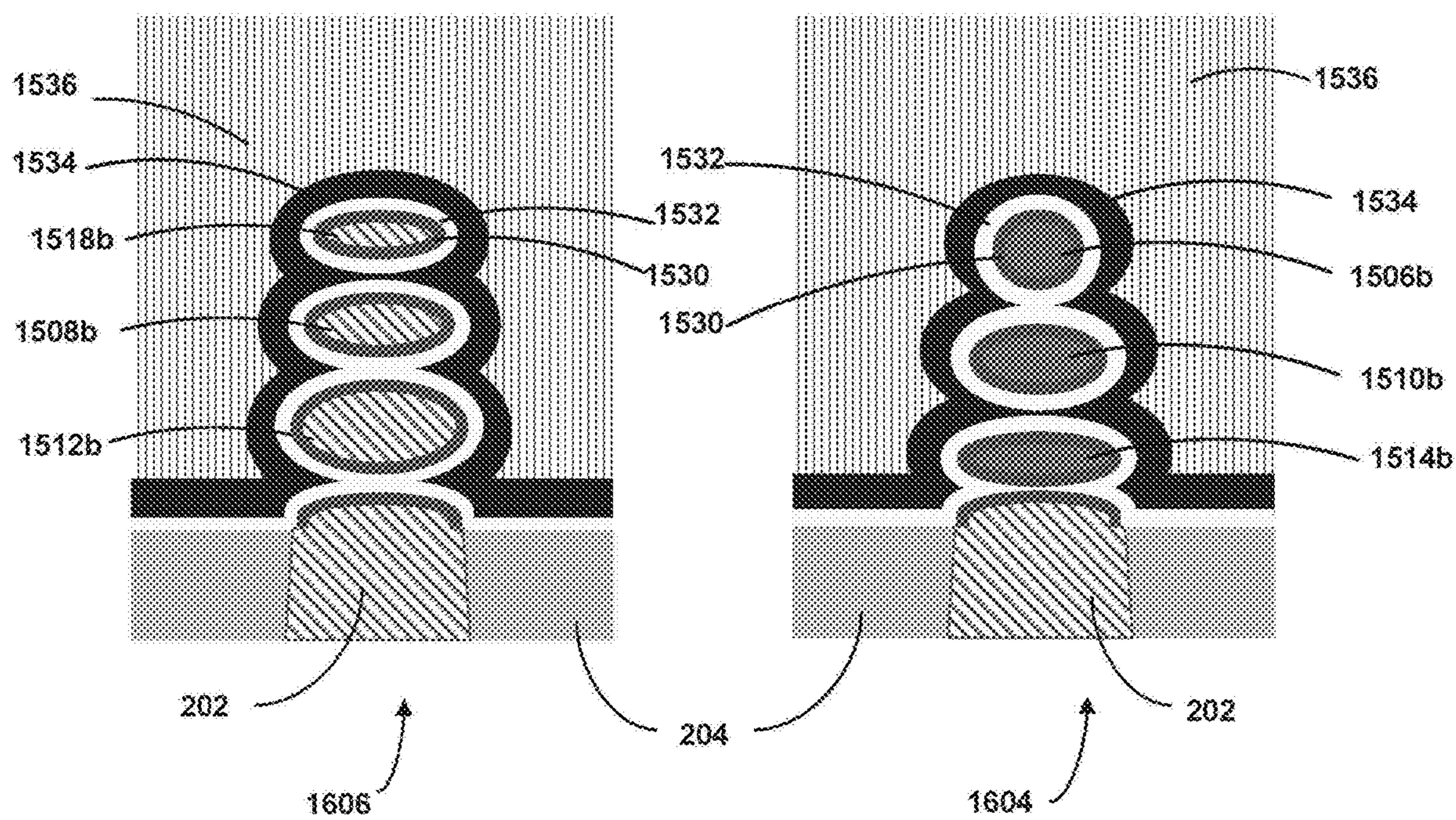


FIG.17

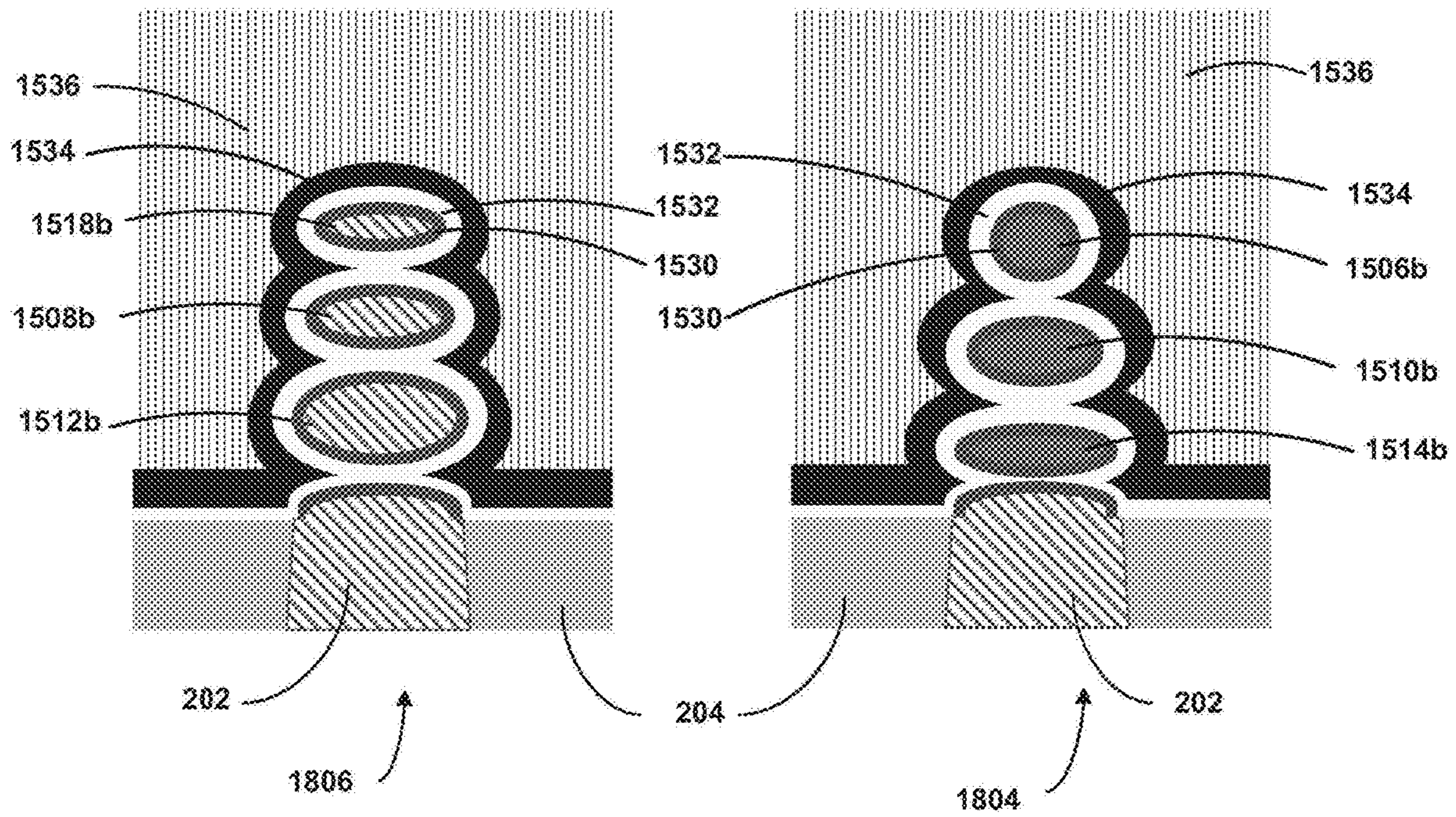


FIG.18

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SILICON AND SILICON GERMANIUM NANOWIRE FORMATION

RELATED APPLICATION

This application is a continuation-in-part of and claims priority to U.S. patent application Ser. No. 16/599,307, titled "SILICON AND SILICON GERMANIUM NANOWIRE FORMATION" and filed on Oct. 11, 2019, which is a continuation of and claims priority to U.S. patent application Ser. No. 16/205,419, titled "SILICON AND SILICON GERMANIUM NANOWIRE FORMATION" and filed on Nov. 30, 2018, which is a continuation of and claims priority to U.S. patent application Ser. No. 15/924,350, titled "SILICON AND SILICON GERMANIUM NANOWIRE FORMATION" and filed on Mar. 19, 2018, now U.S. Pat. No. 10,163,729 issued Dec. 25, 2018, which is a continuation of and claims priority to U.S. patent application Ser. No. 15/463,326, titled "SILICON AND SILICON GERMANIUM NANOWIRE FORMATION" and filed on Mar. 20, 2017, now U.S. Pat. No. 9,935,016 issued Apr. 3, 2018, which is a continuation of and claims priority to U.S. patent application Ser. No. 14/929,504, titled "SILICON AND SILICON GERMANIUM NANOWIRE FORMATION" and filed on Nov. 2, 2015, now U.S. Pat. No. 9,634,091 issued Apr. 25, 2017, which is a divisional of and claims priority to U.S. patent application Ser. No. 13/971,239, titled "SILICON AND SILICON GERMANIUM NANOWIRE FORMATION" and filed on Aug. 20, 2013, now U.S. Pat. No. 9,184,269 issued Nov. 10, 2015, which applications are incorporated herein by reference.

BACKGROUND

A transistor, such as a FinFET transistor, comprises a source region, a drain region, and a channel region between the source region and the drain region. The transistor comprises a gate region that controls the channel region to operate the transistor. The gate region can be formed around one or more surfaces of the channel region, which provides the gate region with increased control over the channel region because the transistor can be controlled by a 3D gate area, as opposed to being controlled merely by a 2D gate area associated with a 2D planar transistor.

DESCRIPTION OF THE DRAWINGS

FIG. 1 is a flow diagram illustrating a method of forming a semiconductor arrangement, according to some embodiments.

FIG. 2 is an illustration of a silicon and silicon germanium stack, according to some embodiments.

FIG. 3 is an illustration of a first source region and a first drain region, according to some embodiments.

FIG. 4 is an illustration of oxidizing a silicon and silicon germanium stack, according to some embodiments.

FIG. 5 is an illustration of a removing silicon oxide region, according to some embodiments.

FIG. 6 is an illustration of a first set of nanostructure field-effect transistors (nano-FETs) comprising a gate structure formed according to a gate-all-around structure, according to some embodiments.

FIG. 7 is an illustration of a first set of nano-FETs, according to some embodiments.

FIG. 8 is an illustration of a silicon and silicon germanium stack, according to some embodiments.

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FIG. 9 is an illustration of a third source region and a third drain region, according to some embodiments.

FIG. 10 is an illustration of a third set of nano-FETs, according to some embodiments.

FIG. 11 is an illustration of an NMOS gate height and a PMOS gate height, according to some embodiments.

FIGS. 12 through 14 are cross-sectional views of intermediate stages in the manufacturing of nano-FETs, in accordance with some embodiments.

FIGS. 15 through 17 are cross-sectional views of intermediate stages in the manufacturing of nano-FETs, in accordance with some embodiments.

FIG. 18 is a cross-sectional view of an intermediate stage in the manufacturing of nano-FETs, in accordance with some embodiments.

DETAILED DESCRIPTION

The claimed subject matter is now described with reference to the drawings, wherein like reference numerals are generally used to refer to like elements throughout. In the following description, for purposes of explanation, numerous specific details are set forth in order to provide an understanding of the claimed subject matter. It is evident, however, that the claimed subject matter can be practiced without these specific details. In other instances, structures and devices are illustrated in block diagram form in order to facilitate describing the claimed subject matter. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed.

Further, spatially relative terms, such as "beneath," "below," "lower," "above," "upper" and the like, may be used herein for ease of description to describe one element or feature's relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

One or more semiconductor arrangements, and one or more techniques for forming such semiconductor arrangements are provided herein. For example, a semiconductor arrangement comprises silicon and silicon germanium stacks that are used to create nano-FETs (e.g., nanostructure such as nanowire, nanosheet, the like, or a combination thereof). In some embodiments, the silicon and silicon germanium stacks create germanium channels for PMOS transistors and silicon channels for NMOS transistors. In some embodiments, the silicon and silicon germanium stacks are tapered stacks such that the width of the stack decreases when moving from the bottom to the top of the stack. In some embodiments, the silicon layers of the stack

have different thicknesses and the thickness of the silicon layers decreases when moving from the bottom silicon layer to the top silicon layer. In some embodiments, the silicon germanium layers of the stack have different thicknesses and the thickness of the silicon layers increases when moving from the bottom silicon germanium layer to the top silicon germanium layer. In an example, the PMOS transistors and the NMOS transistors can be formed during a single fabrication process, such that a PMOS transistor is protected with a hard mask while an NMOS transistor is being processed, and the NMOS transistor is protected with a hard mask while the PMOS transistor is being processed.

To form a germanium nanostructure channel from the silicon and silicon germanium stack for a PMOS transistor, the silicon and silicon germanium stack is oxidized so that the silicon is transformed into a silicon oxide region such as silicon dioxide, resulting in a germanium nanostructure channel. In some embodiments, the germanium nanostructure channel includes a nanowire, a nanosheet, the like, or a combination thereof. In an embodiment, a nanostructure comprising a germanium nanowire channel has a diameter between about 5 nm to about 15 nm. In an embodiment such a diameter is between about 15 nm to about 55 nm. In an embodiment such a diameter is between about 20 nm to about 30 nm. In an embodiment such a diameter is about 6 nm. In an embodiment, a nanostructure comprising a germanium nanowire channel has a length or defines a channel length of between about 15 nm to about 55 nm, where such a channel length is measured from a source region to a drain region of the PMOS transistor. The silicon oxide region can be removed, and a gate structure can be formed around one or more surfaces, such as one, two, three, or all surfaces, of the germanium nanostructure channel.

To form a silicon nanostructure channel from a second silicon and silicon germanium stack for a NMOS transistor, a silicon germanium layer is removed from the second silicon and silicon germanium stack to form a silicon nanostructure channel. In some embodiments, the silicon nanostructure channel includes a nanowire, a nanosheet, the like, or a combination thereof. In an embodiment, a nanostructure comprising a silicon nanowire channel has a diameter between about 5 nm to about 15 nm. In an embodiment such a diameter is between about 15 nm to about 55 nm. In an embodiment such a diameter is between about 20 nm to about 30 nm. In an embodiment such a diameter is about 6 nm. In an embodiment, the silicon nanowire channel has a diameter that is equal to or substantially equal to a diameter of the germanium nanowire channel. In an embodiment, the silicon nanowire channel has a diameter that is larger than a diameter of the germanium nanowire channel. In an embodiment, the silicon nanowire channel has a diameter that is between about 2 nm to about 3 nm larger than a diameter of the germanium nanowire channel. In an embodiment, the silicon nanowire channel has a diameter that is between about 20% to about 40% larger than a diameter of the germanium nanowire channel. In an embodiment, a nanostructure comprising a silicon nanowire channel has a length or defines a channel length of between about 15 nm to about 55 nm, where such a channel length is measured from a source region to a drain region of the NMOS transistor.

In this way, PMOS transistors, comprising germanium nanostructure channels, and NMOS transistors, comprising silicon nanostructure channels, can be formed within the semiconductor arrangement from silicon and silicon germanium stacks. In an example, the semiconductor arrangement has improved current, such as between about 14% to about 16% improved current for NMOS transistors and between

about 13% to about 15% improved current for PMOS transistors. In an example, the semiconductor arrangement has reduced short channel effect, such as between about 6% to about 8% reduction for NMOS transistors and between about 4% to about 6% reduction for PMOS transistors.

In an embodiment, a gate dielectric layer is formed around at least one of the silicon nanostructure channel or the germanium nanostructure channel. In an embodiment, the gate dielectric layer comprises at least one of an interfacial layer (IL) or a high-k dielectric layer (HK layer). In an embodiment, the IL has a thickness between about 5 Å to about 15 Å. In an embodiment, the HK layer has a thickness between about 5 Å to about 20 Å. In an embodiment, at least one of the thickness of the IL around the silicon nanostructure channel or the thickness of the HK layer around the silicon nanostructure channel is less than at least one of the thickness of the IL around the germanium nanostructure channel or the thickness of the HK layer around the germanium nanostructure channel. In an embodiment, at least one of the thickness of the IL around the silicon nanostructure channel or the thickness of the HK layer around the silicon nanostructure channel is between about 5% to about 15% less than at least one of the thickness of the IL around the germanium nanostructure channel or the thickness of the HK layer around the germanium nanostructure channel.

A method **100** of forming a semiconductor arrangement is illustrated in FIG. 1, and one or more semiconductor arrangements formed by such a methodology are illustrated in FIGS. 2-10. A semiconductor arrangement **250** comprises a substrate **202**, as illustrated in embodiment **200** of FIG. 2. In an example, the substrate **202** comprises silicon, and the substrate **202** is formed according to a FinFET arrangement comprising one more silicon fins separated by isolation structures **204**, such as shallow trench isolation (STI). For example, a first fin **202a**, a second fin **202b**, a third fin **202c**, and a fourth fin **202d** are formed from the substrate **202**. In an example, an isolation structure has a depth between about 60 nm to about 120 nm. In an example, a recessed space, between about 50 nm to about 110 nm, is formed into the substrate **202** for formation of silicon and silicon germanium, such as through an epi growth technique, such as chemical vapor deposition (CVD), atomic layer deposition (ALD), vapor phase epitaxy (VPE), molecular beam epitaxy (MBE), or the like, for a silicon and silicon germanium stack where an epi thickness of silicon germanium is between about 5 nm to about 15 nm and an epi thickness for silicon is between about 5 nm to about 15 nm.

At **102**, a silicon and silicon germanium stack is formed over the substrate **202**, as illustrated in embodiment **200** of FIG. 2. For example, a first silicon and silicon germanium stack **220**, a second silicon and silicon germanium stack **222**, or other silicon and silicon germanium stacks not illustrated or identified are formed over the substrate **202**. The first silicon and silicon germanium stack **220** comprises one or more silicon layers and one or more silicon germanium layers. For example, the first silicon and silicon germanium stack **220** comprises a first silicon layer **218**, a first silicon germanium layer **206**, a second silicon layer **208**, a second silicon germanium layer **210**, a third silicon layer **212**, a third silicon germanium layer **214**, and a fourth silicon layer **216**. It is appreciated that any number of silicon layers or silicon germanium layers can be formed. In an example, a silicon germanium layer comprises between about 20% to about 50% germanium.

At **104**, a first source region **302** is formed adjacent to a first side of the first silicon and silicon germanium stack **220**, as illustrated in embodiment **300** of FIG. 3. It is appreciated

that the first source region **302** is illustrated by dashed lines for illustrative purposes so that other portions of the semiconductor arrangement **250** are visible or apparent. At **106**, a first drain region **304** is formed adjacent to a second side of the first silicon and silicon germanium stack **220**, as illustrated in embodiment **300** of FIG. **3**. In an example of forming the first source region **302** and the first drain region **304**, a sacrificial gate is formed, such as a polygate formed by a patterning technique, over the substrate **202** and over the first silicon and silicon germanium stack **220**. Spacers are formed, such as by a deposition technique, on sidewalls of the of the semiconductor arrangement **250**. Portions of the first silicon and silicon germanium stack **220**, corresponding to the first source region **302** and the first drain region **304**, are removed, such as through an etching technique. Source and drain material is formed within the first source region **302** and the first drain region **304**, such as through an epitaxial growth technique, to create a first source and a first drain for a first nanostructure transistor. Other source regions, such as a second source region **306**, and drain regions, such as a second drain region **308**, are formed for other nanostructure transistors that are to be formed for the semiconductor arrangement **250**.

At **108**, the first silicon and silicon germanium stack **220**, illustrated in embodiment **300** of FIG. **3**, is oxidized **402** to form a first oxidized stack **220a**, as illustrated in embodiment **400** of FIG. **4**. In some embodiments, the first silicon and silicon germanium stack **220** or other silicon and silicon germanium stacks are oxidized **402** to form germanium nanostructure channels including a germanium nanowire channel, a germanium nanosheet channel, the like, or a combination thereof. In an example, the second silicon and silicon germanium stack **222**, illustrated in embodiment **300** of FIG. **3**, is oxidized **402** to form a second oxidized stack **222a**, as illustrated in embodiment **400** of FIG. **4**. In an example, the oxidizing **402** comprises removing a sacrificial gate, not illustrated, over the first silicon and silicon germanium stack **220** to expose the first silicon and silicon germanium stack **220** to ambient oxygen. Oxidizing **402** the first silicon and silicon germanium stack **220** transforms silicon, such as silicon of a silicon layer or silicon of a silicon germanium layer, to silicon oxide such as silicon dioxide. For example, the first silicon layer **218** is transformed to a first silicon oxide region **218a**. Silicon of the first silicon germanium layer **206** is transformed to silicon oxide, resulting in a first germanium nanowire channel **206a** between the first source region **302** and the first drain region **304**. The second silicon layer **208** is transformed to a second silicon oxide region **208a**. Silicon of the second silicon germanium layer **210** is transformed into silicon oxide, resulting in a second germanium nanowire channel **210a** between the first source region **302** and the first drain region **304**. The third silicon layer **212** is transformed to a third silicon oxide region **212a**. Silicon of the third silicon germanium layer **214** is transformed into silicon oxide, resulting in a third germanium nanowire channel **214a** between the first source region **302** and the first drain region **304**. The fourth silicon layer **216** is transformed to a fourth silicon oxide region **216a**. In an example, remaining germanium of a silicon and germanium layer is condensed into a germanium nanowire channel. In an example, the first germanium nanowire channel **206a** and the second germanium nanowire channel **210a** are formed such that a space of about 5 nm or greater is between the first germanium nanowire channel **206a** and the second germanium nanowire channel **210a** so that interfacial layer material, high-k dielectric layer material, or titanium nitride capping layer material can be formed

around the first germanium nanowire channel **206a** and the second germanium nanowire channel **210a**. In this way, the first silicon and silicon germanium stack **220** or other silicon and silicon germanium stacks are oxidized **402** to form germanium nanowire channels.

At **110**, silicon oxide, such as a silicon oxide region, is removed, as illustrated in embodiment **500** of FIG. **5**. That is, silicon oxide is removed to expose the germanium nanostructure channels, and to form a region within which a gate structure can be formed. In an example, the first silicon oxide region **218a**, the second silicon oxide region **208a**, the third silicon oxide region **212a**, the fourth silicon oxide region **216a**, or other silicon oxide, such as silicon oxide formed from oxidizing **402** silicon germanium layers, are removed by an etching process **502**. Germanium nanostructure channels, such as the first germanium nanowire channel **206a**, the second germanium nanowire channel **210a**, the third germanium nanowire channel **214a**, or other germanium nanowire channels, can be formed according to various configurations, shapes, or sizes, such as a first germanium nanowire channel **206b** having a cylindrical configuration, a second germanium nanowire channel **210b** having the cylindrical configuration, and a third germanium nanowire channel **214b** having the cylindrical configuration. In this way, source regions, drain regions, and germanium nanowire channels are formed for a first nanostructure transistor **504**, a second nanostructure transistor **506**, or other PMOS nanostructure transistors. The cylindrical configurations of the nanostructure channels can be any cylindrical configuration, such as a circular cylinder, an elliptic cylinder, or the like.

In an example, a first interfacial layer **606** is formed around the first germanium nanowire channel **206b**, a second interfacial layer **610** is formed around the second germanium nanowire channel **210b**, and a third interfacial layer **614** is formed around the third germanium nanowire channel **214b**, as illustrated in embodiment **600** of FIG. **6**. An interfacial layer is formed to improve adhesion between materials or layers. In an example, an interfacial layer comprises nitride, oxide, or other suitable material. In an example, a first high-k dielectric layer **604** is formed around the first interfacial layer **606**, a second high-k dielectric layer **608** is formed around the second interfacial layer **610**, and a third high-k dielectric layer **612** is formed around the third interfacial layer **614**, as illustrated in embodiment **600** of FIG. **6**. In an example, a titanium nitride capping layer is formed around one or more high-k dielectric layers. In an example, a barrier, such as TaN or TiN is formed around the titanium nitride capping layer.

At **112**, a first gate structure **602** is formed around the first germanium nanowire channel **206b**, to form the first nanowire transistors **504**, as illustrated in embodiment **600** of FIG. **6**. In an example, the first gate structure **602** comprises TiN or W, alone or in combination. In the illustrated example, given that there are three germanium nanowire channels, the first gate structure is also formed around the second germanium nanowire channel **210b**, and the third germanium nanowire channel **214b**. In an example, the first gate structure **602** is formed as a gate-all-around structure surrounding the germanium nanowire channels to increase gate control, as illustrated in embodiment **600** of FIG. **6**. In another example, a first gate structure **706** is formed around one or more surfaces of the germanium nanowire channels, as illustrated in embodiment **700** of FIG. **7**. For example, a first interfacial layer **704** is formed around the first germanium nanowire channel **206b**, the second germanium nanowire channel **210b**, and the third germanium nanowire channel

214b. A high-k dielectric layer **702** is formed around the first interfacial layer **704**. The first gate structure **706** is formed around the high-k dielectric layer **702**. In this way, the first gate structure **706** is formed around some, but not all, surfaces of the germanium nanowire channels, which can increase channel density within the first nanowire transistor **504**. The first nanowire transistor **504**, the second nanowire transistor **506**, or other nanowire transistor within the semiconductor arrangement **250** are formed as PMOS transistors, where germanium nanowire channels are formed as P channels for the PMOS transistors. In an example, a first interlayer dielectric is formed over one or more source regions and a second interlayer dielectric is formed over one or more drain regions. In this way, gate structures are formed between the first interlayer dielectric and the second interlayer dielectric. In an example, a blocking layer is formed below the germanium nanowire channels to mitigate punch through or leakage.

In an example, one or more NMOS transistors are formed within the semiconductor arrangement **250** before, during, and/or after formation of the one or more PMOS transistors as a single fabrication process because formation of NMOS transistors and formation of PMOS transistors both utilize silicon and silicon germanium stacks. For example, during at least some of the processes of forming the PMOS transistors, NMOS portion of the semiconductor arrangement **250** are protected by a hard mask. During at least some of the processes of forming the NMOS transistors, PMOS portions of the semiconductor are protected by a hard mask.

FIGS. **8-10** illustrate embodiments of forming one or more NMOS nanostructure transistors within the semiconductor arrangement **250** utilizing silicon and silicon germanium stacks. In an example, the first nanostructure transistor **504**, the second nanostructure transistor **506**, or other nanostructure transistors formed as PMOS transistors within the semiconductor arrangement **250** are protected by a hard mask during formation of the one or more NMOS transistors.

In an example, a third silicon and silicon germanium stack **820**, a fourth silicon and silicon germanium stack **822**, or other silicon and silicon germanium stacks are formed over the substrate **202**, as illustrated in embodiment **800** of FIG. **8**. The third silicon and silicon germanium stack **820** comprises one or more silicon layers and one or more silicon germanium layers. For example, the third silicon and silicon germanium stack **820** comprises a first silicon layer **818**, a first silicon germanium layer **806**, a second silicon layer **808**, a second silicon germanium layer **810**, a third silicon layer **812**, and a third silicon germanium layer **814**. It is appreciated that any number of silicon layers or silicon germanium layers can be formed.

A third source region **902** is formed on a first side of the third silicon and silicon germanium stack **820** and a third drain region **904** is formed on a second side of the third silicon and silicon germanium stack **820**, as illustrated in embodiment **900** of FIG. **9**. In an example, a fourth source region **906**, a fourth drain region **908**, or other source and drain regions are formed adjacent to silicon and silicon germanium stacks. Silicon germanium layers within the silicon and silicon germanium stacks are removed to form silicon nanostructure channels between source regions and drain regions, as illustrated in embodiment **1000** of FIG. **10**. In some embodiments, the silicon germanium layers within the silicon and silicon germanium stacks are removed to form silicon nanostructure channels including a silicon nanowire channel, a silicon nanosheet channel, the like, or a combination thereof. In an example, the first silicon

germanium layer **806** is removed to form a first space **806a** between a first silicon nanowire channel **818a** and a second silicon nanowire channel **808a**, the second silicon germanium layer **810** is removed to form a second space **810a** between the second silicon nanowire channel **808a** and a third silicon nanowire channel **812a**, and the third silicon germanium layer **814** is removed to form a third space **814a** between the third silicon nanowire channel **812a** and the substrate **202**. In an example, a chemical etch **1002** is performed to remove the silicon germanium layers from the silicon and silicon germanium stacks. In an example, the silicon nanowire channels can be formed according to various configurations, shapes, or sizes, such as cylindrical shapes. The cylindrical shapes of the nanostructure channels can be any cylindrical configuration, such as a circular cylinder, an elliptic cylinder, or the like. For example, an oxidation technique or a hydrogen annealing technique is performed to smooth the silicon nanowire channels. In an example, gate structures are formed around the silicon nanowire channels to form a nanostructure nanowire transistor **1004**, a fourth nanostructure transistor **1006**, or other NMOS nanostructure transistors, not illustrated.

In an example, an interfacial layer is formed around one or more of the silicon nanostructure channels. In an example, a high-k dielectric layer is formed around one or more of the silicon nanowire channels or around an interfacial layer if present. A gate structure may be formed as a gate-all-around structure, or around fewer than all sides of a silicon nanowire channel. In an example, the gate structure comprises TiN or W, alone or in combination. Formation of one or more of such gate structures, interfacial layers or high-k dielectric layers is in accordance with that described above with regard to formation of a PMOS transistor, according to some embodiments. In an example, a titanium nitride capping layer is formed around one or more high-k dielectric layers. In an example, a barrier, such as TaN, TiAlC, TaAlC, or TiAl is formed around the titanium nitride capping layer. In an example, gate height for a PMOS nanostructure transistor is less than a gate height for an NMOS nanostructure transistor. In this way, NMOS transistors and PMOS transistors are formed within the semiconductor arrangement **250** utilizing silicon and silicon germanium stacks.

FIG. **11** illustrates an embodiment **1100** of an NMOS gate height **1108** and a PMOS gate height **1114**. A third nanostructure transistor **1004** comprises an NMOS transistor. The third nanostructure transistor **1004** comprises a third source region **902** and a third drain region **904** formed over a substrate **202**. The third nanostructure transistor **1004** comprises a first silicon nanowire channel **818a**, a second silicon nanowire channel **808a**, and a third silicon nanowire channel **812a** formed between the third source region **902** and the third drain region **904**. A first interlayer dielectric **1104** is formed over the third source region **902**, and a second interlayer dielectric **1106** is formed over the third drain region **904**. A gate structure **1102** is formed around the first silicon nanowire channel **818a**, the second silicon nanowire channel **808a**, and the third silicon nanowire channel **812a**. The gate structure **1102** has an NMOS gate height **1108**.

A first nanostructure transistor **504** comprises a PMOS transistor. The first nanowire transistor **504** comprises a first source region **302** and a first drain region **304** formed over the substrate **202**. The first nanostructure transistor **504** comprises a first germanium nanowire channel **206b**, a second germanium nanowire channel **210b**, and a third germanium nanowire channel **214b** formed between the first source region **302** and the first drain region **304**. A third

interlayer dielectric **1110** is formed over the first source region **302**, and a fourth interlayer dielectric **1112** is formed over the first drain region **304**. A first gate structure **706** is formed around the first germanium nanowire channel **206b**, the second germanium nanowire channel **210b**, and the third germanium nanowire channel **214b**. The first gate structure **706** has a PMOS gate height **1114**. In an example, the PMOS gate height **1114** is less than the NMOS gate height **1108**. For example, the PMOS gate height **1114** is less than the NMOS gate height **1108** due to double metal gate CMP used for PMOS.

In an embodiment, a silicon nanostructure to substrate distance **1150** is the same as a germanium nanostructure to substrate distance **1152**, where the silicon nanostructure to substrate distance **1150** is not limited to being relative to the third silicon nanowire channel **812a** and the germanium nanostructure to substrate distance **1152** is not limited to being relative to the third germanium nanowire channel **214b**. In an embodiment, the silicon nanostructure to substrate distance **1150** is larger than the germanium nanostructure to substrate distance **1152**. In an embodiment the silicon nanostructure to substrate distance **1150** is between about 1 nm to about 10 nm larger than the germanium nanostructure to substrate distance **1152**. In an embodiment, at least one of thermal annealing, gate dielectric formation, or threshold voltage adjustment associated with forming a PMOS transistor comprising a germanium nanowire channel can be performed concurrently or substantially concurrently with at least one of thermal annealing, gate dielectric formation, or threshold voltage adjustment associated with forming a NMOS transistor comprising a silicon nanowire channel.

FIGS. **12** through **14** are cross-sectional views of intermediate stages in the manufacturing of nano-FETs (e.g., nanostructure such as nanowire, nanosheet, the like, or a combination thereof), in accordance with some embodiments. FIGS. **12** through **14** illustrate reference cross-section A-A' illustrated in FIGS. **2** and **8**. Cross-section A-A' in FIGS. **2** and **8** are each along a longitudinal axis of a gate electrode and in a direction, for example, perpendicular to the direction of current flow between the epitaxial source/drain regions of the nano-FET.

The embodiment in FIGS. **12** through **14** is similar to the previous embodiments except that this embodiment includes tapered silicon and silicon germanium stacks. In this embodiment, the silicon and silicon germanium stacks are tapered stacks such that the width of the stack decreases when moving from the bottom to the top of the stacks. Details regarding this embodiment that are similar to those for the previously described embodiment will not be repeated herein.

In FIG. **12**, a silicon and silicon germanium stack **1220**, a silicon and silicon germanium stack **1222**, or other silicon and silicon germanium stacks are formed over the substrate/fins **202**, as illustrated. The silicon and silicon germanium stacks **1220** and **1222** comprise one or more silicon layers and one or more silicon germanium layers. For example, the silicon and silicon germanium stack **1220** comprises a first silicon layer **1218**, a first silicon germanium layer **1206**, a second silicon layer **1208**, a second silicon germanium layer **1210**, a third silicon layer **1212**, and a third silicon germanium layer **1214**. It is appreciated that any number of silicon layers or silicon germanium layers can be formed.

In the embodiment of FIGS. **12** through **15**, the silicon and silicon germanium stacks **1220** and **1222** are tapered stacks such that the width of the stack decreases when moving from the bottom to the top of the stacks. Each of the stacks **1220** and **1222** may have widths at the top of the stack of **W1**, with

W1 being in a range from about 3 nm to about 15 nm, such as about 7 nm. Each of the stacks **1220** and **1222** may have widths at the bottom of the stack of **W2**, with **W2** being in a range from about 6 nm to about 20 nm, such as about 10 nm. The widths **W1** and **W2** are measured in a direction parallel to a major surface of the substrate **202**.

Further, in the embodiment of FIGS. **12** through **15**, the silicon germanium layers **1206**, **1210**, and **1214** each have a same thickness **T1** in a range from about 5 nm to about 30 nm, such as about 15 nm, and the silicon layers **1218**, **1208**, and **1212** each have a same thickness **T2** in a range from about 5 nm to about 30 nm, such as about 15 nm. The thicknesses **T1** and **T2** are measured in a direction perpendicular to a major surface of the substrate **202**.

In this embodiment, the silicon and silicon germanium stack **1220** will be subsequently utilized in a PMOS nanostructure transistor, and the silicon and silicon germanium stack **1222** will be subsequently utilized in an NMOS nanostructure transistor. In some embodiments, the nanostructure transistors include one or more nanostructure channels including a nanowire, a nanosheet, the like, or a combination thereof.

FIG. **13** illustrates an intermediate stage of processing with the nanostructure channels formed. The processing between FIGS. **12** and **13** is similar to that described in FIGS. **2** through **5** and FIGS. **8-10** above and the description of forming this intermediate stage of processing is not repeated herein.

In FIG. **13**, the silicon layers of the silicon and silicon germanium stack **1220** are removed to expose the germanium nanostructure channels, and to form a region within which a gate structure can be formed. In an example, the first silicon layer **1218**, the second silicon layer **1208**, and the third silicon layer **1212**, or other silicon layer are removed by an etching process. In some embodiments, the etching process may be a wet etching process including etchants such as, tetramethylammonium hydroxide (TMAH), ammonium hydroxide (NH₄OH), or the like. Germanium nanostructure channels can be formed according to various configurations, shapes, or sizes, such as a first germanium nanostructure channel **1206b** having a cylindrical configuration, a second germanium nanostructure channel **1210b** having the cylindrical configuration, and a third germanium nanostructure channel **1214b** having the cylindrical configuration. In this way, source regions, drain regions, and germanium nanostructure channels are formed for a first PMOS nanostructure transistor **1304** or other PMOS nanostructure transistor. The cylindrical configurations of the nanostructure channels can be any cylindrical configuration, such as a circular cylinder, an elliptic cylinder, or the like.

In some embodiments, the first germanium nanostructure channel **1206b** has a width **W4**, the second germanium nanostructure channel **1210b** has a width **W5**, and the third germanium nanostructure channel **1214b** has a width **W6**, with each of the widths being measured in a direction parallel to a major surface of the substrate **202**. In some embodiments, the width **W4** is less than **W5** and the width **W5** is less than **W6**.

Further in FIG. **13**, the silicon germanium layers of the silicon and silicon germanium stack **1222** are removed to expose the silicon nanostructure channels, and to form a region within which a gate structure can be formed. In an example, the first silicon germanium layer **1206**, the second silicon germanium layer **1210**, and the third silicon germanium layer **1214**, or other silicon germanium layer are removed by an etching process. In some embodiments, the etching process may be a wet etching process including

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etchants such as, TMAH, NH_4OH , or the like. Silicon nanostructure channels can be formed according to various configurations, shapes, or sizes, such as a first silicon nanostructure channel **1218b** having a cylindrical configuration, a second silicon nanostructure channel **1208b** having the cylindrical configuration, and a third silicon nanostructure channel **1212b** having the cylindrical configuration. In this way, source regions, drain regions, and silicon nanostructure channels are formed for a first NMOS nanostructure transistor **1306** or other NMOS nanostructure transistor. The cylindrical configurations of the nanostructure channels can be any cylindrical configuration, such as a circular cylinder, an elliptic cylinder, or the like.

In some embodiments, the first silicon nanostructure channel **1218b** has a width **W7**, the second silicon nanostructure channel **1208b** has a width **W8**, and the third silicon nanostructure channel **1212b** has a width **W9**, with each of the widths being measured in a direction parallel to a major surface of the substrate **202**. In some embodiments, the width **W7** is less than **W8** and the width **W8** is less than **W9**.

In FIG. **14**, interfacial layers **1230**, gate dielectric layers **1232**, work function layers **1234**, and gate electrodes **1236** are formed for replacement gates. The interfacial layers **1230** are formed conformally on the nanostructure channels. In some embodiments, the interfacial layers **1230** comprise nitride, oxide, or other suitable material.

The gate dielectric layers **1232** are deposited conformally over the nanostructure channels. The interfacial layer **1230** may also be considered a gate dielectric layers and the gate dielectric layers may be referred to as **1230/1232**. In the first NMOS nanostructure transistor **1306**, the gate dielectric layers **1232** may be formed on top surfaces and sidewalls of the substrate/fins **202** and on top surfaces, sidewalls, and bottom surfaces of the silicon nanostructure channels **1218b**, **1208b**, and **1212b**, and in the first PMOS nanostructure transistor **1304**, the gate dielectric layers **1232** may be formed on top surfaces and sidewalls of the substrate/fins **202** and on top surfaces, sidewalls, and bottom surfaces of the germanium nanostructure channels **1206b**, **1210b**, and **1214b**. The gate dielectric layers **1232** may also be deposited on top surfaces of dielectric layers, such as an interlayer dielectric, spacers, and isolation structures **204**.

In accordance with some embodiments, the gate dielectric layers **1232** comprise one or more dielectric layers, such as an oxide, a metal oxide, the like, or combinations thereof. For example, in some embodiments, the gate dielectrics may comprise a silicon oxide layer and a metal oxide layer over the silicon oxide layer. In some embodiments, the gate dielectric layers **1232** include a high-k dielectric material, and in these embodiments, the gate dielectric layers **1232** may have a k value greater than about 7.0, and may include a metal oxide or a silicate of hafnium, aluminum, zirconium, lanthanum, manganese, barium, titanium, lead, and combinations thereof. The structure of the gate dielectric layers **1232** may be the same or different in the first NMOS nanostructure transistor **1306** and the first PMOS nanostructure transistor **1304**. The formation methods of the gate dielectric layers **1232** may include molecular-beam deposition (MBD), ALD, PECVD, and the like.

The work function layers (also referred to as liner layers) **1234** are deposited over the gate dielectric layers **1232**. The work function layers **1234** may be formed conformally over the gate dielectric layers **1232**. The work function layers **1234** may include a metal-containing material such as titanium nitride, titanium oxide, tantalum nitride, tantalum carbide, cobalt, ruthenium, aluminum, tungsten, combina-

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tions thereof, or multi-layers thereof. The work function layers **1234** may comprise any number of liner layers and any number of work function tuning layers.

The gate electrodes **1236** are deposited over the work function layers **1234** and fill the remaining portions of the recesses around the nanostructure channels. The work function layers **1234** may also be considered a gate electrode layer and the gate electrodes may be referred to as **1234/1236**. The gate electrodes **1236** may include a metal-containing material such as titanium nitride, titanium oxide, tantalum nitride, tantalum carbide, cobalt, ruthenium, aluminum, tungsten, combinations thereof, or multi-layers thereof. For example, although single layer gate electrodes **1236** are illustrated in FIG. **14**, the gate electrodes **1236** may comprise any number of fill material layers. Any combination of the layers which make up the gate electrodes **1236** may be deposited in the first NMOS nanostructure transistor **1306** between adjacent ones of the silicon nanostructure channels **1218b**, **1208b**, **1212b** and the substrate/fin **202**, and may be deposited in the first PMOS nanostructure transistor **1304** between adjacent ones of the germanium nanostructure channels **1206b**, **1210b**, **1214b**, and the substrate/fin **202**. The gate electrodes **1232**, the work function layers **1234**, the gate dielectric layers **1232**, and the interfacial layers **1230** may be collectively referred to as "gate structures."

In this embodiment, the gate dielectric layers **1230/1232** merges between adjacent nanostructure channels such that the work function layers **1234** and the gate electrodes **1236** do not completely surround each of the nanostructure channels. In this way, the gate structures are formed around some, but not all, surfaces of the silicon and germanium nanostructure channels, which can increase channel density within the first NMOS nanostructure transistor **1306** and the first PMOS nanostructure transistor **1304**. The spacing between the adjacent nanostructure channels is largely determined on the thickness of the layers of the silicon and silicon germanium stacks as they are formed. For example, the thinner the layers are formed, the smaller the spacing and the more likely the gate dielectric layers **1230/1232** will merge between adjacent nanostructure channels. In this embodiment where the gate dielectric layers **1230/1232** merges between adjacent nanostructure channels, the thickness of the removed layers of the silicon and silicon germanium stacks (e.g., the silicon layers **1218**, **1208**, and **1212** in first PMOS nanostructure transistor **1304** and the silicon germanium layers **1206**, **1210**, and **1214** in first NMOS nanostructure transistor **1306**) is less than two times the of the combined thickness of the interfacial layer **1230** and the gate dielectric layer **1232**.

The formation of the gate dielectric layers **1230/1232** in first NMOS nanostructure transistor **1306** and first PMOS nanostructure transistor **1304** may occur simultaneously such that the gate dielectric layers **1230/1232** in each region are formed from the same materials, and the formation of the gate electrodes **1234/1236** may occur simultaneously such that the gate electrodes **1234/1236** in each region are formed from the same materials. In some embodiments, the gate dielectric layers **1230/1232** in each region may be formed by distinct processes, such that the gate dielectric layers **1230/1232** may be different materials and/or have a different number of layers, and/or the gate electrodes **1234/1236** in each region may be formed by distinct processes, such that the gate electrodes **1234/1236** may be different materials and/or have a different number of layers. Various masking steps may be used to mask and expose appropriate regions when using distinct processes.

After depositing the gate electrodes **1236**, a planarization process, such as a CMP, may be performed to remove the excess portions of the gate dielectric layers **1230/1232** and the material of the gate electrodes. The remaining portions of material of the gate electrodes **1234/1236** and the gate dielectric layers **1230/1232** thus form replacement gate structures of the resulting first NMOS nanostructure transistor **1306** and first PMOS nanostructure transistor **1304**.

FIGS. **15** through **17** are cross-sectional views of intermediate stages in the manufacturing of nano-FETs, in accordance with some embodiments. FIGS. **15** through **17** illustrate reference cross-section A-A' illustrated in FIGS. **2** and **8**. Cross-section A-A' in FIGS. **2** and **8** are each along a longitudinal axis of a gate electrode and in a direction, for example, perpendicular to the direction of current flow between the epitaxial source/drain regions of the nano-FET.

The embodiment in FIGS. **15** through **17** is similar to the previous embodiment of FIGS. **12** through **14** except that this embodiment includes silicon and silicon germanium stacks with the silicon and silicon germanium layers having different thicknesses. Details regarding this embodiment that are similar to those for the previously described embodiment will not be repeated herein.

In FIG. **15**, a silicon and silicon germanium stack **1520**, a silicon and silicon germanium stack **1522**, or other silicon and silicon germanium stacks are formed over the substrate/fins **202**, as illustrated. The silicon and silicon germanium stack **1520** and **1522** comprise one or more silicon layers and one or more silicon germanium layers. For example, the silicon and silicon germanium stack **1520** comprises a first silicon layer **1518**, a first silicon germanium layer **1506**, a second silicon layer **1508**, a second silicon germanium layer **1510**, a third silicon layer **1512**, and a third silicon germanium layer **1514**. It is appreciated that any number of silicon layers or silicon germanium layers can be formed.

In the embodiment of FIGS. **15** through **17**, the silicon layers **1518**, **1508**, and **1512** of the stacks **1520** and **1522** have different thicknesses. In a specific embodiment, thicknesses of the silicon layers **1518**, **1508**, and **1512** decreases when moving from the bottom to the top of the stacks. The first silicon layer **1518** has a thickness **T3** in a range from about 3 nm to about 10 nm, such as about 5 nm. The second silicon layer **1508** has a thickness **T4** in a range from about 5 nm to about 15 nm, such as about 10 nm. The third silicon layer **1512** has a thickness **T5** in a range from about 10 nm to about 20 nm, such as about 15 nm. In some embodiments, **T3** is less than **T4** and **T4** is less than **T5**. The thicknesses **T3**, **T4**, and **T5** are measured in a direction perpendicular to a major surface of the substrate **202**.

Further, in this embodiment, the silicon germanium layers **1506**, **1510**, and **1514** of the stacks **1520** and **1522** have different thicknesses. In a specific embodiment, thicknesses of the silicon germanium layers **1506**, **1510**, and **1514** increases when moving from the bottom to the top of the stacks. The first silicon germanium layer **1506** has a thickness **T6** in a range from about 10 nm to about 20 nm, such as about 15 nm. The second silicon germanium layer **1510** has a thickness **T7** in a range from about 5 nm to about 15 nm, such as about 10 nm. The third silicon germanium layer **1514** has a thickness **T8** in a range from about 3 nm to about 10 nm, such as about 5 nm. In some embodiments, **T6** is greater than **T7** and **T7** is greater than **T8**. The thicknesses **T6**, **T7**, and **T8** are measured in a direction perpendicular to a major surface of the substrate **202**.

In this embodiment, the silicon and silicon germanium stack **1520** will be subsequently utilized in a PMOS nano-

structure transistor, and the silicon and silicon germanium stack **1522** will be subsequently utilized in an NMOS nanostructure transistor.

FIG. **16** illustrates an intermediate stage of processing with the nanostructure channels formed. The processing between FIGS. **15** and **16** is similar to that described in FIGS. **2** through **5** and FIGS. **8-10** above and the description of forming this intermediate stage of processing is not repeated herein.

In FIG. **16**, the silicon layers of the silicon and silicon germanium stack **1520** are removed to expose the germanium nanostructure channels, and to form a region within which a gate structure can be formed. In an example, the first silicon layer **1518**, the second silicon layer **1508**, and the third silicon layer **1512**, or other silicon layer are removed by an etching process. In some embodiments, the etching process may be a wet etching process including etchants such as, TMAH, NH_4OH , or the like. Germanium nanostructure channels can be formed according to various configurations, shapes, or sizes, such as a first germanium nanostructure channel **1506b** having a cylindrical configuration, a second germanium nanostructure channel **1510b** having the cylindrical configuration, and a third germanium nanostructure channel **1514b** having the cylindrical configuration. In this way, source regions, drain regions, and germanium nanostructure channels are formed for a first PMOS nanostructure transistor **1604** or other PMOS nanostructure transistor.

In some embodiments, the first germanium nanostructure channel **1506b** has a thickness **T10**, the second germanium nanostructure channel **1510b** has a thickness **T11**, and the third germanium nanostructure channel **1514b** has a thickness **T10**, with each of the thicknesses being measured in a direction perpendicular to a major surface of the substrate **202**. In some embodiments, the thickness **T10** is greater than thickness **T11** and the thickness **T11** is greater than thickness **T12**.

Further in FIG. **16**, the silicon germanium layers of the silicon and silicon germanium stack **1522** are removed to expose the silicon nanostructure channels, and to form a region within which a gate structure can be formed. In an example, the first silicon germanium layer **1506**, the second silicon germanium layer **1510**, and the third silicon germanium layer **1514**, or other silicon germanium layer are removed by an etching process. In some embodiments, the etching process may be a wet etching process including etchants such as, TMAH, NH_4OH , or the like. Silicon nanostructure channels can be formed according to various configurations, shapes, or sizes, such as a first silicon nanostructure channel **1518b** having a cylindrical configuration, a second silicon nanostructure channel **1508b** having the cylindrical configuration, and a third silicon nanostructure channel **1512b** having the cylindrical configuration. In this way, source regions, drain regions, and silicon nanostructure channels are formed for a first NMOS nanostructure transistor **1606** or other NMOS nanostructure transistor.

In some embodiments, the first silicon nanostructure channel **1518b** has a thickness **T13**, the second silicon nanostructure channel **1508b** has a thickness **T14**, and the third silicon nanostructure channel **1512b** has a thickness **T15**, with each of the thicknesses being measured in a direction perpendicular to a major surface of the substrate **202**. In some embodiments, the thickness **T13** is less than thickness **T14** and the thickness **T14** is less than thickness **T15**.

In FIG. **17**, interfacial layers **1530**, gate dielectric layers **1532**, work function layers **1534**, and gate electrodes **1536**

are formed for replacement gates. The interfacial layers **1530**, gate dielectric layers **1532**, work function layers **1534**, and gate electrodes **1536** are similar to the interfacial layers **1230**, the gate dielectric layers **1232**, the work function layers **1234**, and the gate electrodes **1236**, respectively, described above and the description is not repeated herein. formed conformally on the nanostructure channels.

In this embodiment, the gate dielectric layers **1530/1532** merges between some of the adjacent nanostructure channels such that the work function layers **1234** and the gate electrodes **1236** do not completely surround some of the nanostructure channels. Also, in this embodiment, the gate dielectric layers **1530/1532** do not merge between some of the adjacent nanostructure channels such that the work function layers **1234** and the gate electrodes **1236** do completely surround some of the nanostructure channels. The spacing between the adjacent nanostructure channels is largely determined on the thickness of the layers of the silicon and silicon germanium stacks as they are formed. For example, the thinner the layers are formed, the smaller the spacing and the more likely the gate dielectric layers **1230/1232** will merge between adjacent nanostructure channels.

In this embodiment, the thickness **T6** of the silicon germanium layer **1506** is greater than two times the of the combined thickness of the interfacial layer **1530** and the gate dielectric layer **1532** such that the gate dielectric layer **1530/1532** do not merge between the silicon nanostructure channels **1518b** and **1508b** in the NMOS nanostructure transistor **1606**. In this embodiment, the thicknesses **T7** and **T8** of the silicon germanium layers **1510** and **1514**, respectively, is less than two times the of the combined thickness of the interfacial layer **1530** and the gate dielectric layer **1532** such that the gate dielectric layer **1530/1532** does merge between the silicon nanostructure channels **1508b** and **1512b** and the substrate/fin **202** in the NMOS nanostructure transistor **1606**.

In this embodiment, the thickness **T5** of the silicon layer **1512** is greater than two times the of the combined thickness of the interfacial layer **1530** and the gate dielectric layer **1532** such that the gate dielectric layer **1530/1532** do not merge between the silicon germanium nanostructure channels **1514b** and **1510b** in the PMOS nanostructure transistor **1604**. In this embodiment, the thicknesses **T4** and **T3** of the silicon layers **1508** and **1518**, respectively, is less than two times the of the combined thickness of the interfacial layer **1530** and the gate dielectric layer **1532** such that the gate dielectric layer **1530/1532** does merge between the silicon germanium nanostructure channels **1510b** and **1506b** in the PMOS nanostructure transistor **1604**.

FIG. **18** is a cross-sectional view of an intermediate stages in the manufacturing of nano-FETs, in accordance with some embodiments. FIG. **18** illustrates reference cross-section A-A' illustrated in FIGS. **2** and **8**. Cross-section A-A' in FIGS. **2** and **8** are each along a longitudinal axis of a gate electrode and in a direction, for example, perpendicular to the direction of current flow between the epitaxial source/drain regions of the nano-FET.

The embodiment in FIG. **18** is similar to the previous embodiment of FIGS. **15** through **17** except that in this embodiment the gate dielectric layers **1530/1532** merge between each of the nanostructure channels. Details regarding this embodiment that are similar to those for the previously described embodiment will not be repeated herein.

In this embodiment, the thicknesses **T3** through **T8** are different similar to the previous embodiment, but in this embodiment, the thicknesses **T3** through **T8** are tuned to have the gate dielectric layers **1530/1532** merge between

each of the nanostructure channels. This can be accomplished by reducing each of the thicknesses to be less than two times the of the combined thickness of the interfacial layer **1530** and the gate dielectric layer **1532** such that the gate dielectric layer **1530/1532** merges between adjacent nanostructure channels. In this way, the gate structures are formed around some, but not all, surfaces of the silicon and germanium nanostructure channels, which can increase channel density within the NMOS nanostructure transistor **1806** and the first PMOS nanostructure transistor **1804**.

According to an aspect of the instant disclosure, a semiconductor arrangement is provided. The semiconductor arrangement comprises a first nanostructure transistor, such as a PMOS transistor. The first nanostructure transistor comprises a first germanium nanostructure channel formed between a first source region and a first drain region. The first nanostructure transistor comprises a first gate structure formed around the first germanium nanostructure channel. The semiconductor arrangement comprises a second nanostructure transistor, such as an NMOS transistor. The second nanostructure transistor comprises a first silicon nanostructure channel formed between a second source region and a second drain region

According to an aspect of the instant disclosure, a method for forming a semiconductor arrangement is provided. The method comprises forming a first silicon and silicon germanium stack over a substrate. The first silicon and silicon germanium stack comprises a first silicon layer and a first silicon germanium layer. A first source region is formed adjacent to a first side of the first silicon and silicon germanium stack. A first drain region is formed adjacent to a second side of the first silicon and silicon germanium stack. The first silicon and silicon germanium stack is oxidized to form a first germanium nanostructure channel. The oxidizing comprises transforming the first silicon layer and silicon of the first silicon and germanium layer into a silicon oxide region. The first germanium nanostructure channel is formed between the first source region and the first drain region. The silicon oxide region is removed. A first gate structure is formed around the first germanium nanostructure channel to form a first nanostructure transistor. A second nanostructure transistor comprising a first silicon nanostructure channel is formed within the semiconductor arrangement.

According to an aspect of the instant disclosure, a semiconductor arrangement is provided. The semiconductor arrangement comprises a PMOS nanostructure transistor. The PMOS nanostructure transistor comprises a first germanium nanostructure channel formed between a first source region and a first drain region. The PMOS nanostructure transistor comprises a first gate structure formed around the first germanium nanostructure channel. The semiconductor arrangement comprises an NMOS nanostructure transistor. The NMOS nanostructure transistor comprises a first silicon nanostructure channel formed between a second source region and a second drain region. The NMOS nanostructure transistor comprises a second gate structure formed around the first silicon nanostructure channel.

Although the subject matter has been described in language specific to structural features or methodological acts, it is to be understood that the subject matter of the appended claims is not necessarily limited to the specific features or acts described above. Rather, the specific features and acts described above are disclosed as embodiment forms of implementing at least some of the claims.

Various operations of embodiments are provided herein. The order in which some or all of the operations are

described should not be construed to imply that these operations are necessarily order dependent. Alternative ordering will be appreciated given the benefit of this description. Further, it will be understood that not all operations are necessarily present in each embodiment provided herein. 5 Also, it will be understood that not all operations are necessary in some embodiments.

It will be appreciated that layers, features, elements, etc. depicted herein are illustrated with particular dimensions relative to one another, such as structural dimensions or orientations, for example, for purposes of simplicity and ease of understanding and that actual dimensions of the same differ substantially from that illustrated herein, in some embodiments. Additionally, a variety of techniques exist for forming the layers features, elements, etc. mentioned herein, such as etching techniques, implanting techniques, doping techniques, spin-on techniques, sputtering techniques such as magnetron or ion beam sputtering, growth techniques, such as thermal growth or deposition techniques such as chemical vapor deposition (CVD), physical vapor deposition (PVD), plasma enhanced chemical vapor deposition (PECVD), or atomic layer deposition (ALD), for example.

Further, unless specified otherwise, “first,” “second,” or the like are not intended to imply a temporal aspect, a spatial aspect, an ordering, etc. Rather, such terms are merely used as identifiers, names, etc. for features, elements, items, etc. For example, a first channel and a second channel generally correspond to channel A and channel B or two different or two identical channels or the same channel.

Moreover, “exemplary” is used herein to mean serving as an example, instance, illustration, etc., and not necessarily as advantageous. As used in this application, “or” is intended to mean an inclusive “or” rather than an exclusive “or”. In addition, “a” and “an” as used in this application are generally to be construed to mean “one or more” unless specified otherwise or clear from context to be directed to a singular form. Also, at least one of A and B or the like generally means A or B or both A and B. Furthermore, to the extent that “includes”, “having”, “has”, “with”, or variants thereof are used, such terms are intended to be inclusive in a manner similar to “comprising”.

Also, although the disclosure has been shown and described with respect to one or more implementations, equivalent alterations and modifications will occur to others skilled in the art based upon a reading and understanding of this specification and the annexed drawings. The disclosure includes all such modifications and alterations and is limited only by the scope of the following claims. In particular regard to the various functions performed by the above described components (e.g., elements, resources, etc.), the terms used to describe such components are intended to correspond, unless otherwise indicated, to any component which performs the specified function of the described component (e.g., that is functionally equivalent), even though not structurally equivalent to the disclosed structure. In addition, while a particular feature of the disclosure may have been disclosed with respect to only one of several implementations, such feature may be combined with one or more other features of the other implementations as may be desired and advantageous for any given or particular application.

What is claimed is:

1. A semiconductor device comprising:
 - a first nanostructure transistor over a substrate, the first nanostructure transistor comprising:

- a first nanostructure channel extending from a first source region to a first drain region, the first nanostructure channel having a first width;
- a second nanostructure channel extending from the first source region to the first drain region, the second nanostructure channel being over the first nanostructure channel, the second nanostructure channel having a second width less than the first width;
- a first dielectric layer surrounding the first nanostructure channel and the second nanostructure channel;
- a first gate electrode over the first dielectric layer and at least partially surrounding the first nanostructure channel and the second nanostructure channel;
- an interfacial layer surrounding the first nanostructure channel and the second nanostructure channel, the interfacial layer being between the first dielectric layer and the first nanostructure channel and the second nanostructure channel; and
- a first work function layer over the first dielectric layer and at least partially surrounding the first nanostructure channel and the second nanostructure channel, the first work function layer being between the first gate electrode and the first dielectric layer.

2. The semiconductor device of claim 1, wherein the first work function layer completely surrounds the second nanostructure channel and only partially surrounds the first nanostructure channel.

3. The semiconductor device of claim 1, wherein the first nanostructure channel and the second nanostructure channel are germanium nanostructure channels.

4. The semiconductor device of claim 1, wherein the first nanostructure channel and the second nanostructure channel are silicon nanostructure channels.

5. The semiconductor device of claim 1, wherein a space between the first nanostructure channel and the second nanostructure channel is void of the first gate electrode.

6. The semiconductor device of claim 1, wherein the first nanostructure channel has a first thickness, the first thickness being measured in a direction perpendicular to the first width, wherein the second nanostructure channel has a second thickness, the second thickness being measured in a direction perpendicular to the second width, the second thickness being greater than the first thickness.

7. The semiconductor device of claim 1 further comprising:

- a second nanostructure transistor over the substrate, the second nanostructure transistor comprising:
 - a third nanostructure channel extending from a second source region to a second drain region, the third nanostructure channel having a third width;
 - a fourth nanostructure channel extending from the second source region to the second drain region, the fourth nanostructure channel being over the third nanostructure channel, the fourth nanostructure channel having a fourth width less than the third width;
 - a second dielectric layer surrounding the third nanostructure channel and the fourth nanostructure channel; and
 - a second gate electrode over the second dielectric layer and at least partially surrounding the third nanostructure channel and the fourth nanostructure channel.

8. The semiconductor device of claim 7, wherein the first nanostructure channel comprises a different material composition than the third nanostructure channel.

9. The semiconductor device of claim 7, wherein a distance from the substrate to a lowermost nanostructure

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channel of the first nanostructure transistor is less than a distance from the substrate to a lowermost nanostructure channel of the second nanostructure transistor.

10. The semiconductor device of claim 7, wherein the first nanostructure channel comprises germanium and the third nanostructure channel comprises silicon.

11. The semiconductor device of claim 1, wherein the first nanostructure transistor further comprises:

a fifth nanostructure channel extending from the first source region to the first drain region, the fifth nanostructure channel being over the second nanostructure channel, the fifth nanostructure channel having a fifth width, the fifth width being less than the second width.

12. The semiconductor device of claim 11, wherein the first dielectric layer merges between the fifth nanostructure channel and the second nanostructure channel, and wherein the first dielectric layer does not merge between the first nanostructure channel and the second nanostructure channel.

13. A semiconductor device comprising:

a PMOS nanostructure transistor comprising:

a plurality of first nanosheets over a first fin, the plurality of first nanosheets being nanosheets of a first semiconductor material, each of the plurality of first nanosheets having a different width;

first source/drain regions on opposing ends of the plurality of first nanosheets;

a first dielectric layer surrounding each of the plurality of first nanosheets;

a first work function layer over the first dielectric layer; and

a first gate fill over the first work function layer; and

an NMOS nanostructure transistor comprising:

a plurality of second nanosheets over a second fin, the plurality of second nanosheets being nanosheets of a second semiconductor material different than the first semiconductor material, each of the plurality of second nanosheets having a different width;

second source/drain regions on opposing ends of the plurality of second nanosheets;

a second dielectric layer surrounding each of the plurality of second nanosheets;

a second work function layer over the second dielectric layer; and

a second gate fill over the second work function layer, wherein an upper nanosheet of the plurality of first nanosheets is thicker than a lower nanosheet of the plurality of first nanosheets, and wherein an upper nanosheet of the plurality of second nanosheets is thinner than a lower nanosheet of the plurality of second nanosheets, the thicknesses of the plurality of first and second nanosheets being measured in a direction perpendicular to the widths of the plurality of first and second nanosheets.

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14. The semiconductor device of claim 13, wherein the plurality of first nanosheets comprise a plurality of germanium nanosheets.

15. The semiconductor device of claim 13, wherein the first work function layer completely surrounds the lower nanosheet of the plurality of first nanosheets, and wherein the first work function layer does not completely surround the upper nanosheet the plurality of first nanosheets.

16. The semiconductor device of claim 15, wherein the second work function layer completely surrounds the upper nanosheet of the plurality of second nanosheets, and wherein the second work function layer does not completely surround the lower nanosheet the plurality of second nanosheets.

17. A method comprising:

forming a first silicon and silicon germanium stack over a substrate, the first silicon and silicon germanium stack comprising a first silicon layer and a first silicon germanium layer, the first silicon and silicon germanium stack having a first width at a bottom of the stack and a second width at a top of the stack, the second width being less than the first width;

forming a first source region on a first end of the first silicon and silicon germanium stack;

forming a first drain region on a second end of the first silicon and silicon germanium stack;

removing the first silicon layer forming a first germanium nanostructure channel between the first source region and the first drain region;

forming a first interfacial layer surrounding the first germanium nanostructure channel;

forming a first dielectric layer surrounding the first interfacial layer;

forming a first gate structure around the first dielectric layer forming a first nanostructure transistor, the first gate structure comprising a first work function layer and a first gate electrode; and

forming a second nanostructure transistor comprising a first silicon nanostructure channel.

18. The method of claim 17 further comprising:

forming a second germanium nanostructure channel in the first nanostructure transistor, the second germanium nanostructure channel having a different width than the first germanium nanostructure channel.

19. The method of claim 17 further comprising:

forming a second silicon nanostructure channel in the second nanostructure transistor, the second silicon nanostructure channel having a different width than the first silicon nanostructure channel.

20. The semiconductor device of claim 13, wherein the plurality of second nanosheets comprise a plurality of silicon nanosheets.

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